

EE 330

Lecture 27

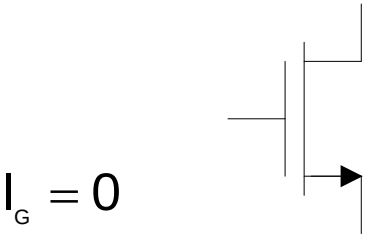
- Small-Signal Analysis
 - Graphical Interpretation
 - MOSFET Model Extensions
 - Biasing (a precursor)

Two-Port Amplifier Modeling

Fall 2025 Exam Schedule

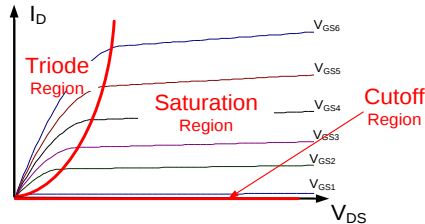
Exam 1	Friday	Sept 26
Exam 2	Friday	October 24
Exam 3	Friday	Nov 21
Final Exam	Monday	Dec 15 12:00 - 2:00 PM

Small Signal Model of MOSFET



Large Signal Model

3-terminal device



$$I_D = \begin{cases} 0 & V_{GS} \leq V_T \\ \mu C_{OX} \frac{W}{L} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) V_{DS} & V_{GS} \geq V_T, V_{DS} < V_{GS} - V_T \\ \mu C_{OX} \frac{W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS}) & V_{GS} \geq V_T, V_{DS} \geq V_{GS} - V_T \end{cases}$$

$$V_{GS} \leq V_T$$

$$V_{GS} \geq V_T \quad V_{DS} < V_{GS} - V_T$$

$$V_{GS} \geq V_T \quad V_{DS} \geq V_{GS} - V_T$$

MOSFET is usually operated in saturation region in linear applications where a small-signal model is needed so will develop the small-signal model in the saturation region

Small Signal Model of MOSFET

Saturation Region Summary

Nonlinear model:

$$\left\{ \begin{array}{l} I_D = \mu C_{\text{ox}} \frac{W}{2L} (V_{\text{GS}} - V_{\text{T}})^2 (1 + \lambda V_{\text{DS}}) \\ I_G = 0 \end{array} \right.$$

Small-signal model:

$$\left\{ \begin{array}{l} i_G = y_{11} v_{\text{GS}} + y_{12} v_{\text{DS}} = 0 \\ i_D = y_{21} v_{\text{GS}} + y_{22} v_{\text{DSE}} \end{array} \right.$$

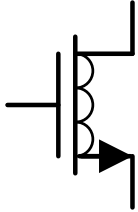
$$y_{11} = 0$$

$$y_{12} = 0$$

$$y_{21} = g_m \cong \mu C_{\text{ox}} \frac{W}{L} (V_{\text{GSQ}} - V_{\text{T}})$$

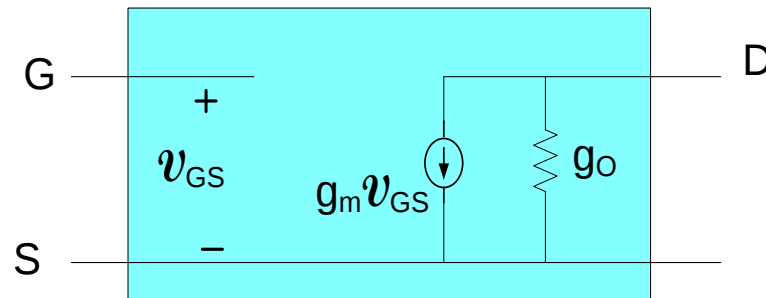
$$y_{22} = g_o \cong \lambda I_{\text{DQ}}$$

Small-Signal Model of MOSFET



$$g_m = \mu C_{\text{ox}} \frac{W}{L} (V_{\text{GSQ}} - V_T)$$

$$g_o \cong \lambda I_{\text{DQ}}$$



Alternate equivalent expressions for g_m :

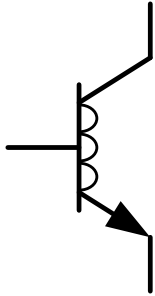
$$I_{\text{DQ}} = \mu C_{\text{ox}} \frac{W}{2L} (V_{\text{GSQ}} - V_T)^2 (1 + \lambda V_{\text{DSQ}}) \cong \mu C_{\text{ox}} \frac{W}{2L} (V_{\text{GSQ}} - V_T)^2$$

$$g_m = \mu C_{\text{ox}} \frac{W}{L} (V_{\text{GSQ}} - V_T)$$

$$g_m = \sqrt{2\mu C_{\text{ox}} \frac{W}{L}} \cdot \sqrt{I_{\text{DQ}}}$$

$$g_m = \frac{2I_{\text{DQ}}}{V_{\text{GSQ}} - V_T}$$

Small Signal Model of BJT



$$\begin{aligned} i_B &= y_{11} v_{BE} + y_{12} v_{CE} \\ i_C &= y_{21} v_{BE} + y_{22} v_{CE} \end{aligned}$$

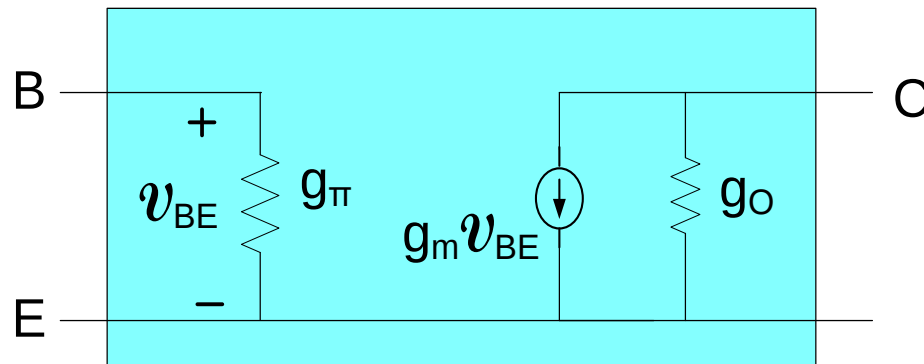


$$\begin{aligned} i_B &= g_{\pi} v_{BE} \\ i_C &= g_m v_{BE} + g_o v_{CE} \end{aligned}$$

$$g_{\pi} = \frac{I_{CQ}}{\beta V_t}$$

$$g_m = \frac{I_{CQ}}{V_t}$$

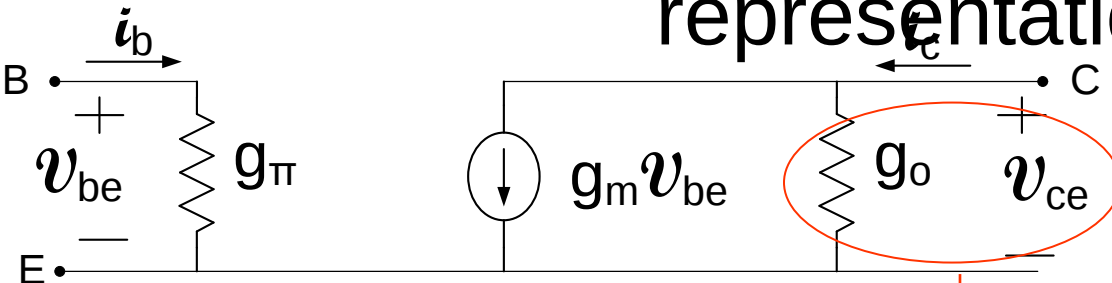
$$g_o = \frac{I_{CQ}}{V_{AF}}$$



An equivalent circuit

y-parameter model using “g” parameter notation

Small Signal BJT Model – alternate representation

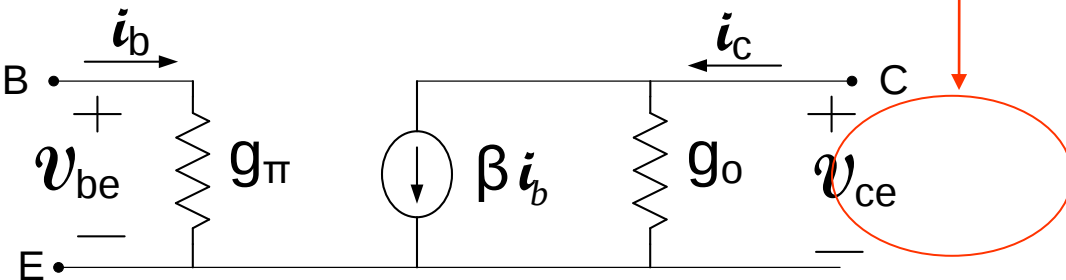


$$g_m = \frac{I_{CQ}}{V_t}$$

$$g_{\pi} = \frac{I_{CQ}}{\beta V_t}$$

$$g_o \cong \frac{I_{CQ}}{V_{AF}}$$

Alternate equivalent small signal model

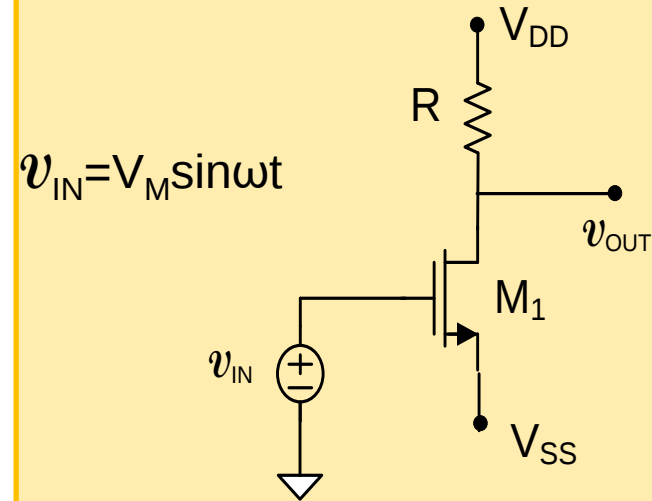


$$g_{\pi} = \frac{I_{CQ}}{\beta V_t}$$

$$g_o \cong \frac{I_{CQ}}{V_{AF}}$$

Consider again: Review from last lecture

Small-signal analysis example

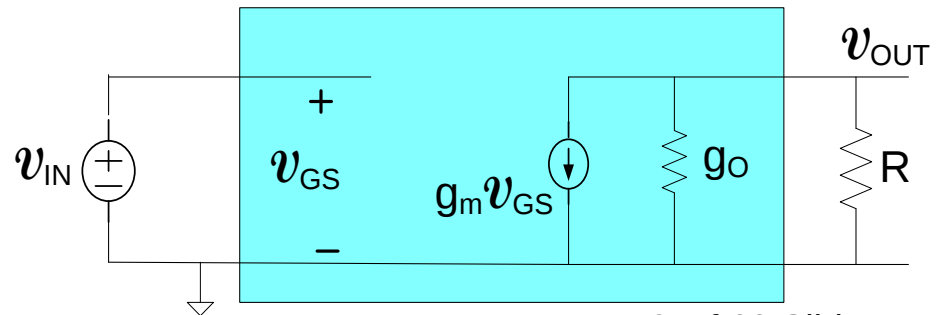
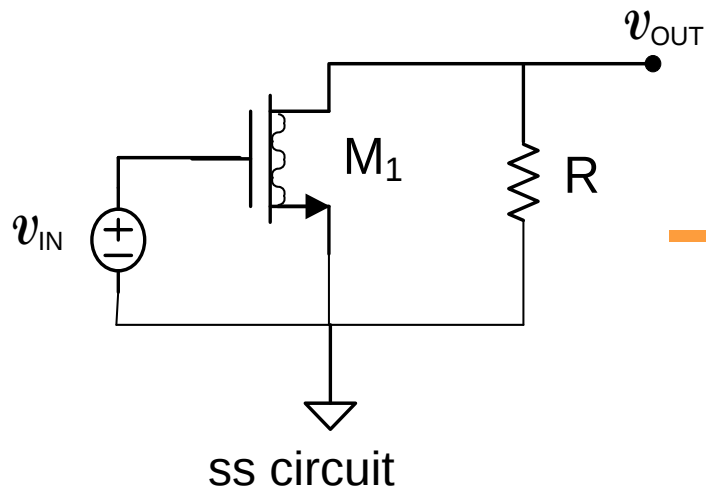


$$A_v = \frac{2I_{DQ} R}{[V_{SS} + V_T]}$$

Derived for $\lambda=0$ (equivalently $g_o=0$)

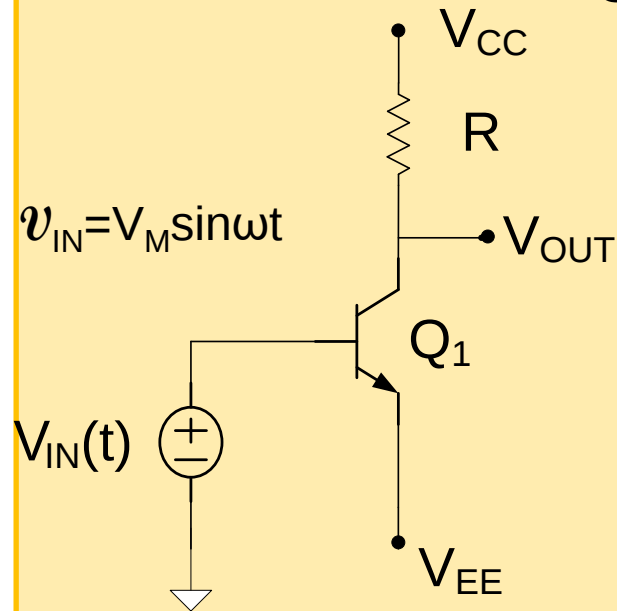
$$I_D = \mu C_{ox} \frac{W}{2L} (V_{GS} - V_T)^2$$

Recall the derivation was very tedious and time consuming!



Consider again: Review from last lecture

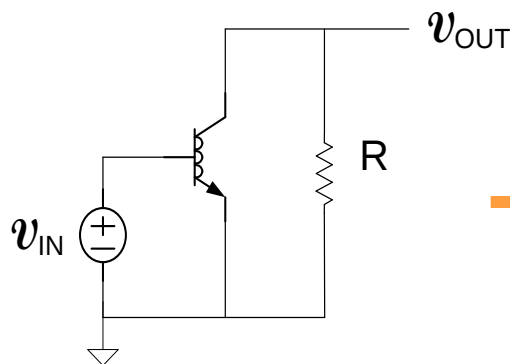
Small signal analysis example



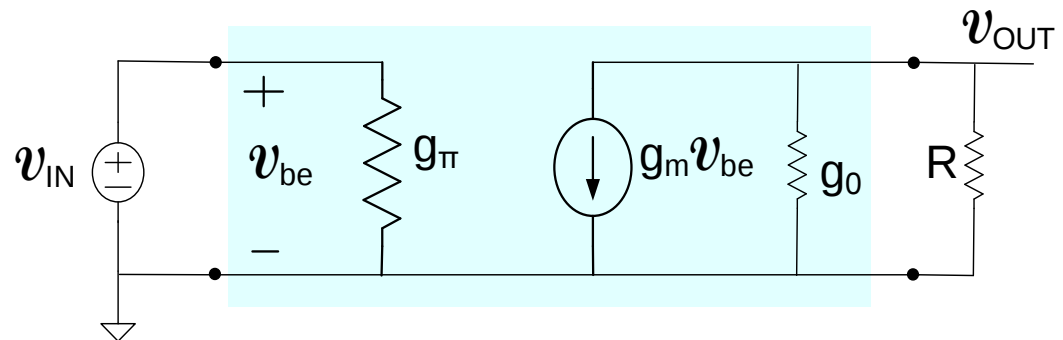
$$A_{vB} = - \frac{I_{CQ} R}{V_t}$$

Derived for $V_{AF}=0$ (equivalently $g_o=0$)

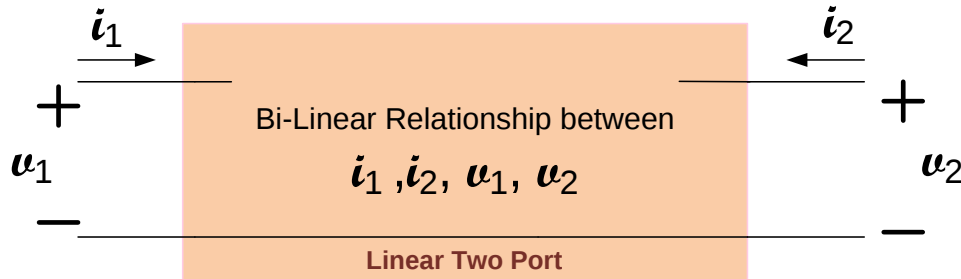
Recall the derivation was very tedious and time consuming!



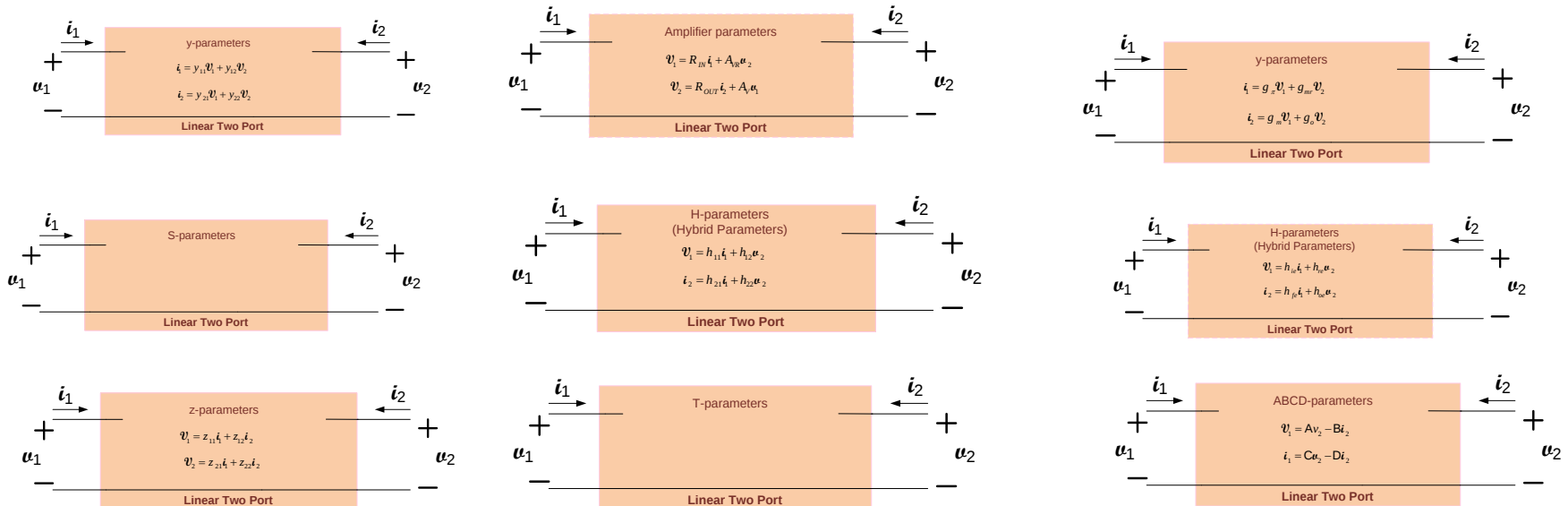
ss circuit



Small-Signal Model Representations



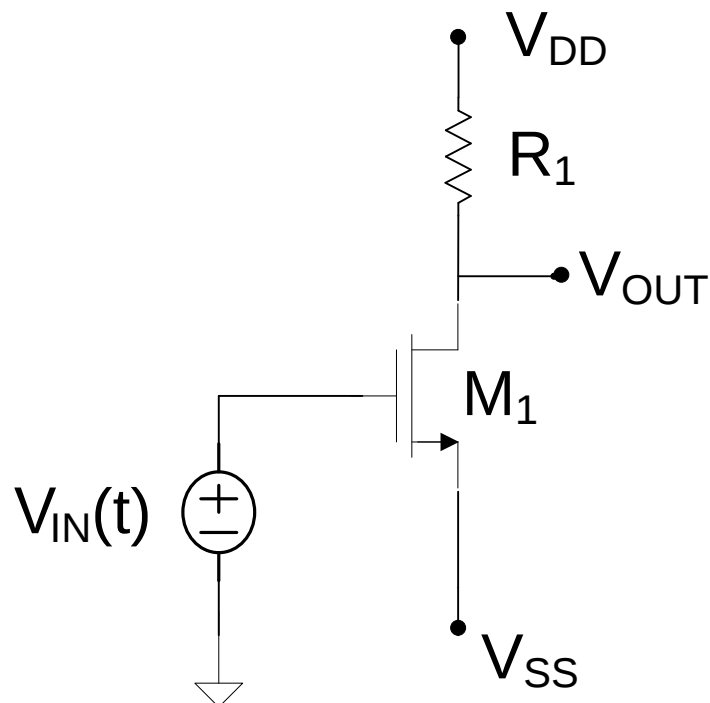
The good, the bad, and the **unnecessary** !!



- Equivalent circuits often given for each representation
- All provide identical characterization
- Easy to move from any one to another

Graphical Analysis and Interpretation

Consider Again



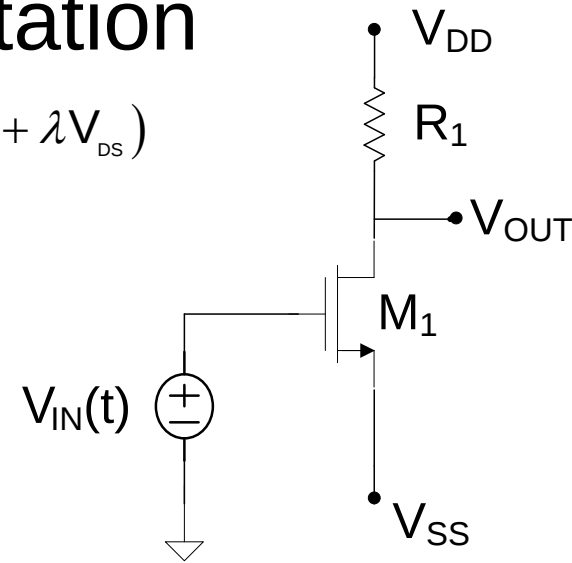
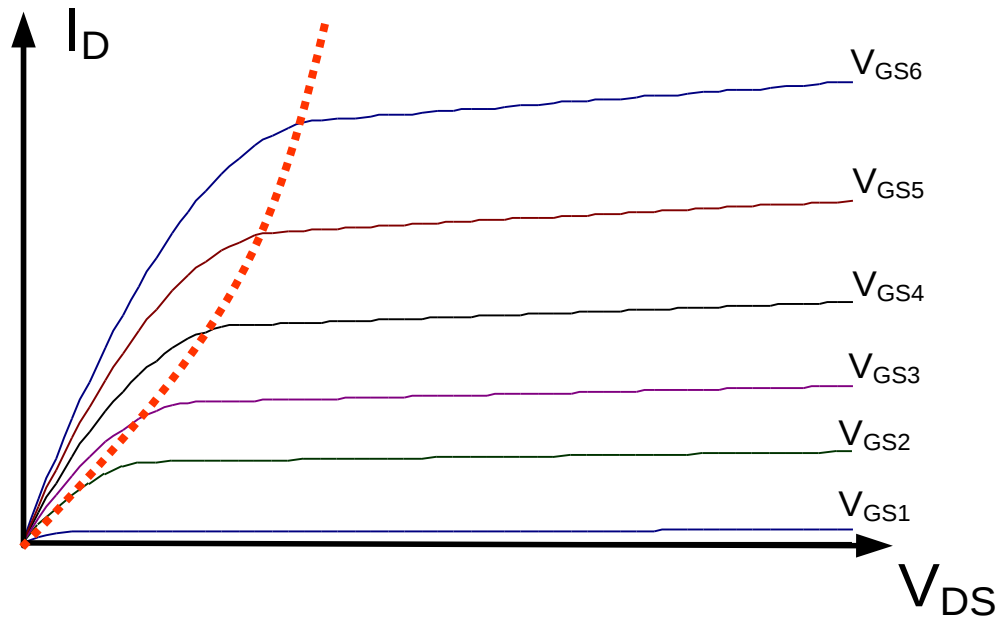
$$V_{OUT} = V_{DD} - I_D R$$

$$I_D = \frac{\mu C_{OX} W}{2L} (V_{IN} - V_{SS} - V_T)^2$$

$$I_{DQ} = \frac{\mu C_{OX} W}{2L} (V_{SS} + V_T)^2$$

Graphical Analysis and Interpretation

Device Model (family of curves)
$$I_D = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$



Load Line



$$V_{OUT} = V_{DD} - I_D R$$

Device Model



$$I_D = \frac{\mu C_{ox} W}{2L} (V_{IN} - V_{SS} - V_T)^2$$

Device Model at Operating Point

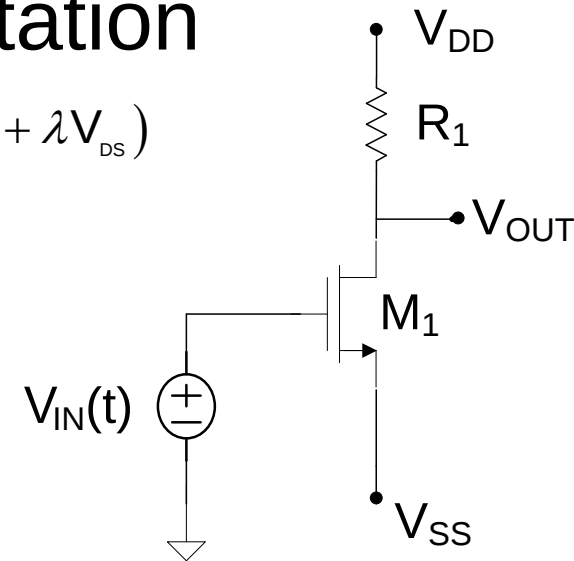
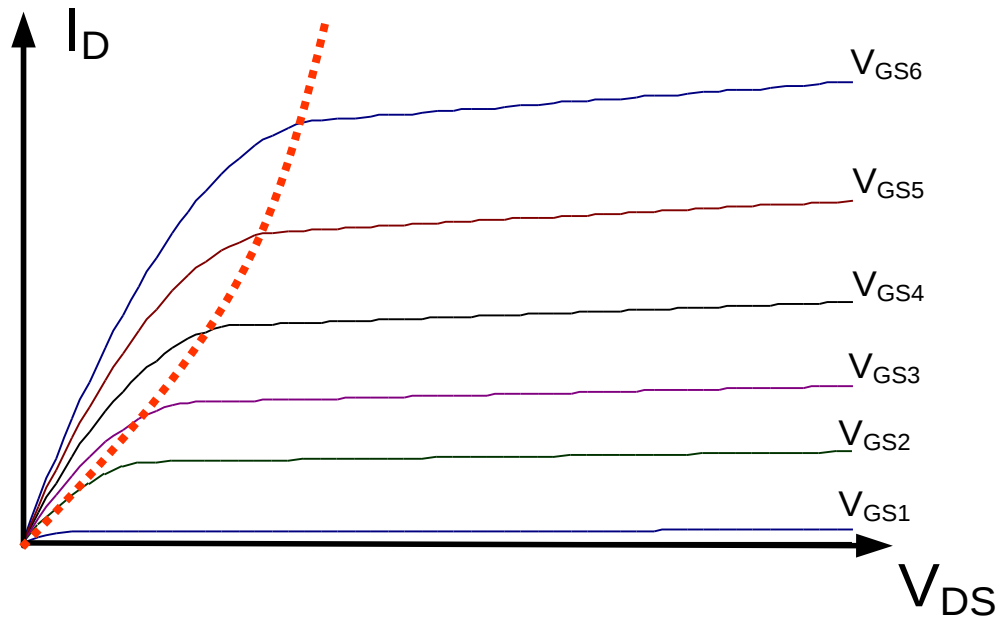


$$I_{DQ} = \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

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Graphical Analysis and Interpretation

Device Model (family of curves)
$$I_D = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$



$$V_{OUT} = V_{DD} - I_D R$$

$$V_{SS} + V_{DS} = V_{DD} - I_D R$$

Load Line



Device Model



Device Model at Operating Point



$$V_{OUT} = V_{DD} - I_D R$$

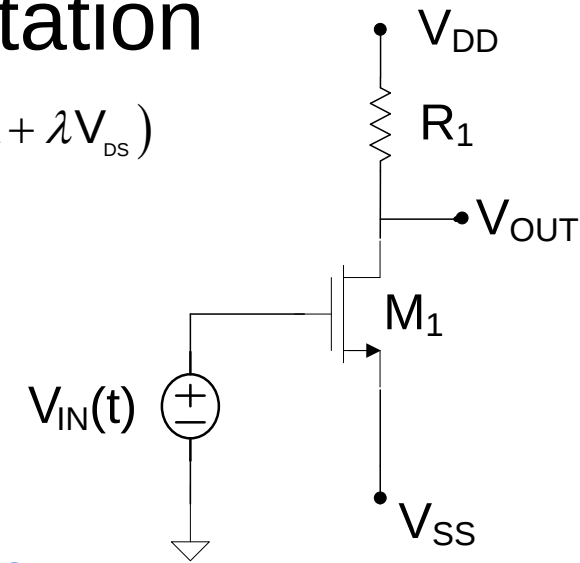
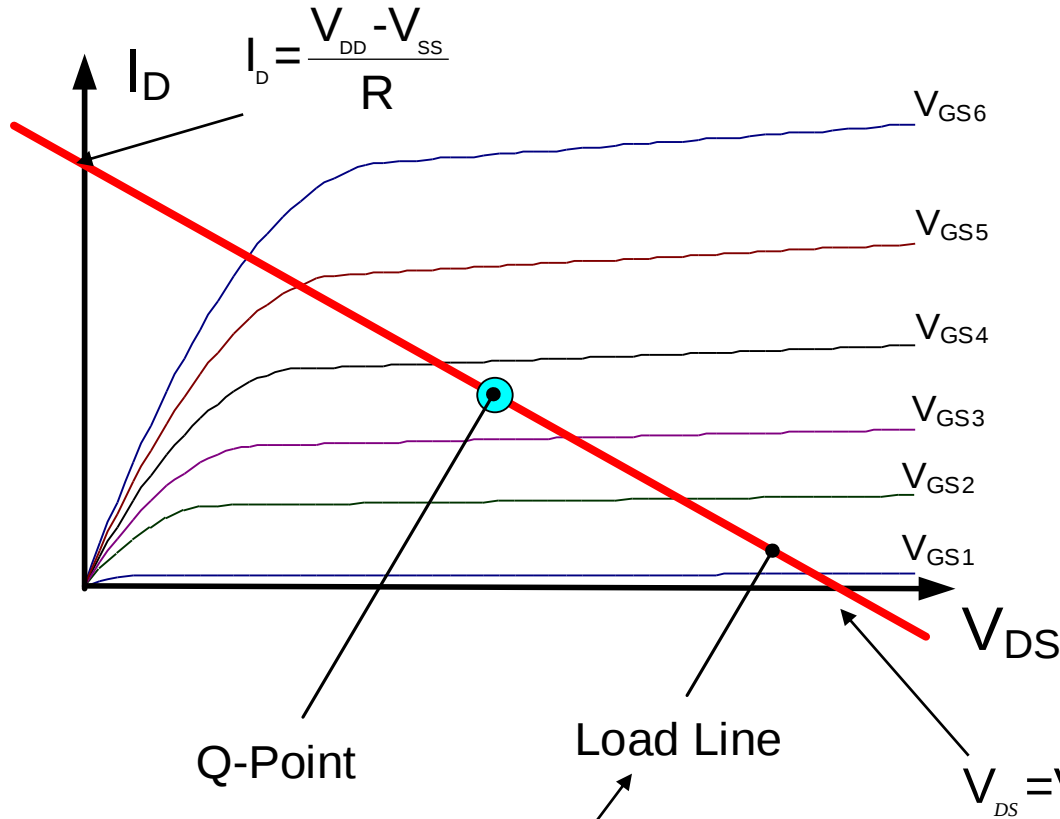
$$I_D = \frac{\mu C_{ox} W}{2L} (V_{IN} - V_{SS} - V_T)^2$$

$$I_{DQ} = \frac{\mu C_{ox} W}{2L} (V_{SS} + V_{15})^2$$

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Graphical Analysis and Interpretation

Device Model (family of curves) $I_D = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$



$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

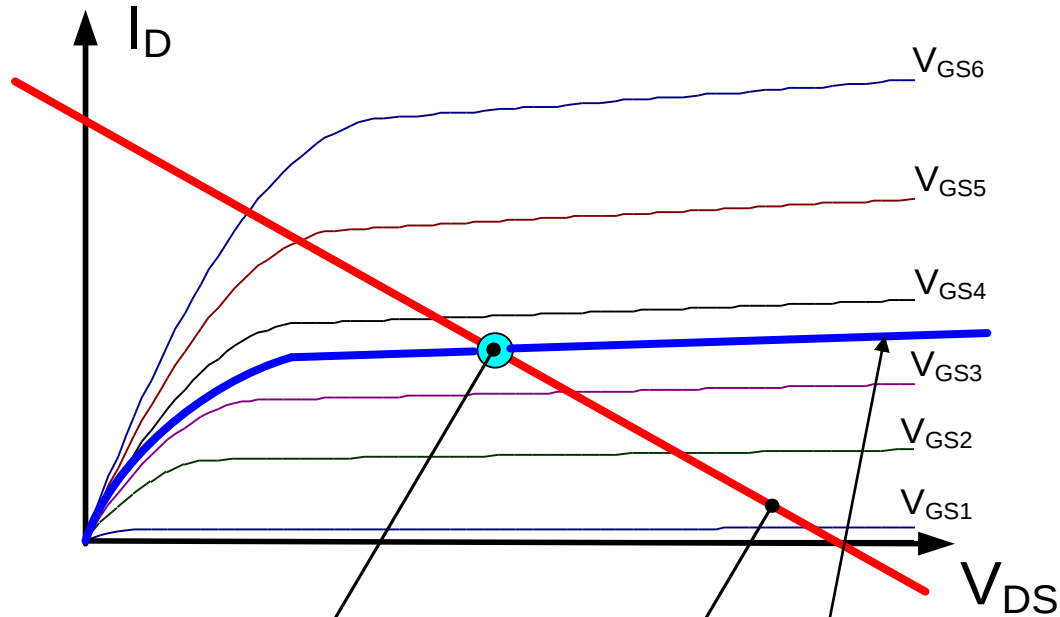
$$V_{GSQ} = -V_{SS}$$

$$V_{SS} + V_{DS} = V_{DD} - I_D R$$

$$I_D = \frac{\mu C_{ox} W}{2L} (V_{IN} - V_{SS} - V_T)^2 \quad ?$$

Graphical Analysis and Interpretation

Device Model (family of curves) $I_D = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$



$$V_{GSQ} = -V_{SS}$$

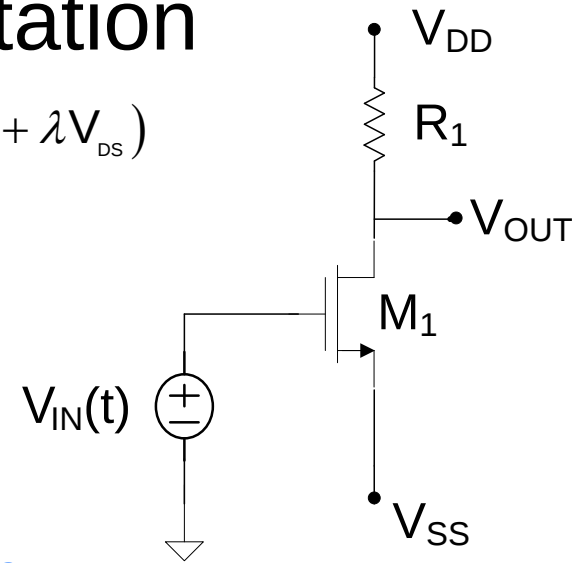
$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

$$V_{GSQ} = -V_{SS}$$

$$V_{OUT} = V_{DD} - I_D R$$

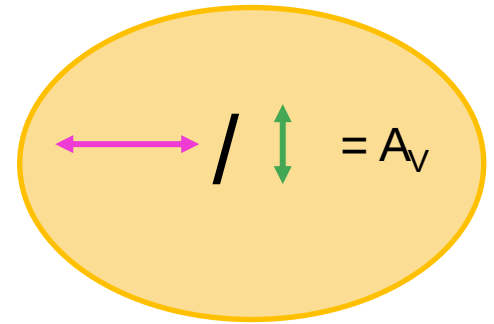
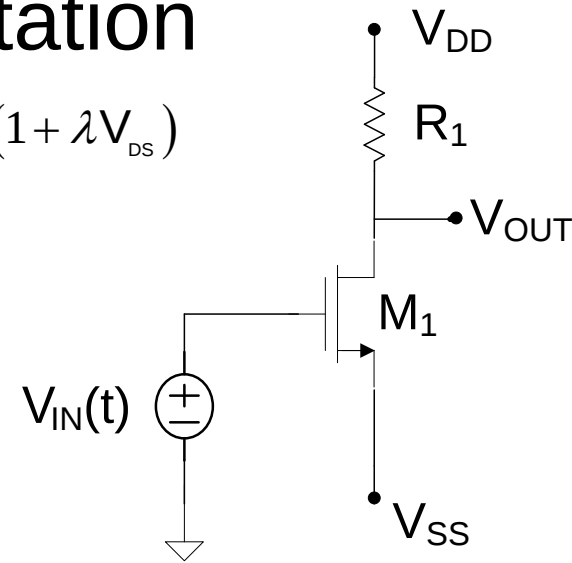
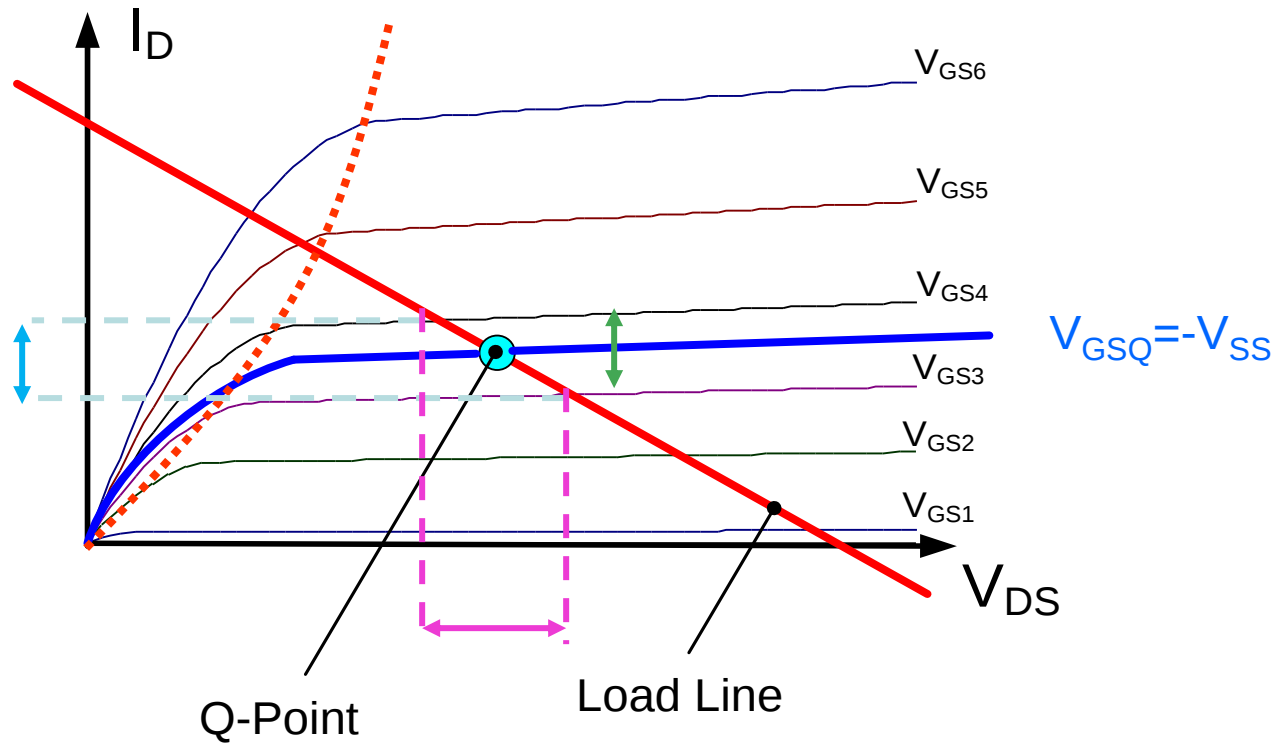
$$I_D = \frac{\mu C_{ox} W}{2L} (V_{IN} - V_{SS} - V_T)^2 \quad ?$$

Must satisfy both equations
all of the time !



Graphical Analysis and Interpretation

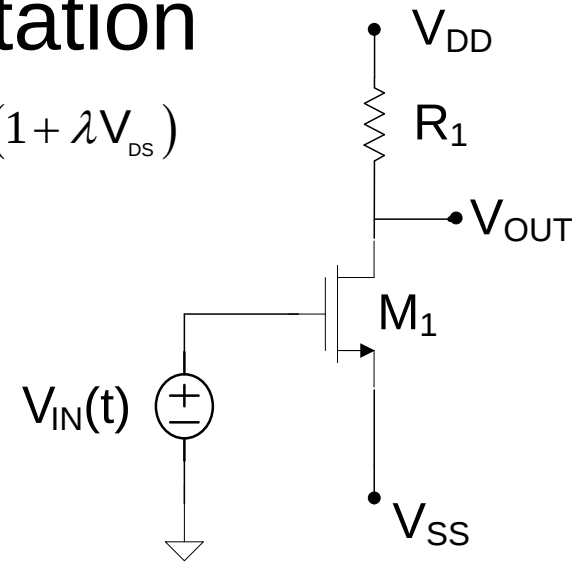
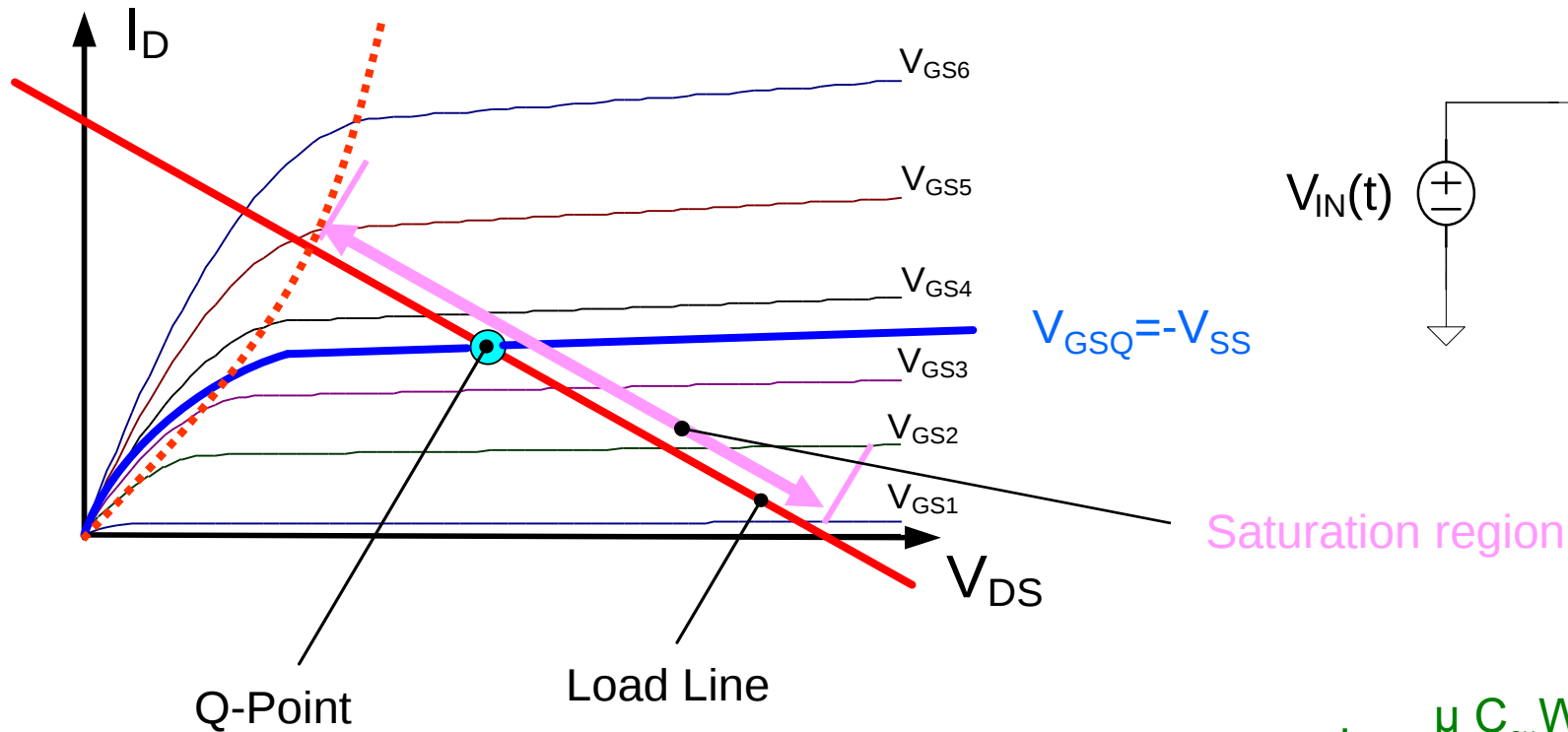
Device Model (family of curves)
$$I_D = \frac{\mu C_{ox} W}{2L} (V_{IN} - V_{SS} - V_T)^2 (1 + \lambda V_{DS})$$



- As V_{IN} changes around Q-point, V_{IN} induces changes in V_{GS} . The operating point must remain on the load line!
- Small sinusoidal changes of V_{IN} will be nearly symmetric around the V_{GSQ} line
- This will cause nearly symmetric changes in both I_D and V_{DS} !
- Since V_{SS} is constant, change in V_{DS} is equal to change in V_{OUT}

Graphical Analysis and Interpretation

Device Model (family of curves) $I_D = \frac{\mu C_{ox} W}{2L} (V_{IN} - V_{SS} - V_T)^2 (1 + \lambda V_{DS})$

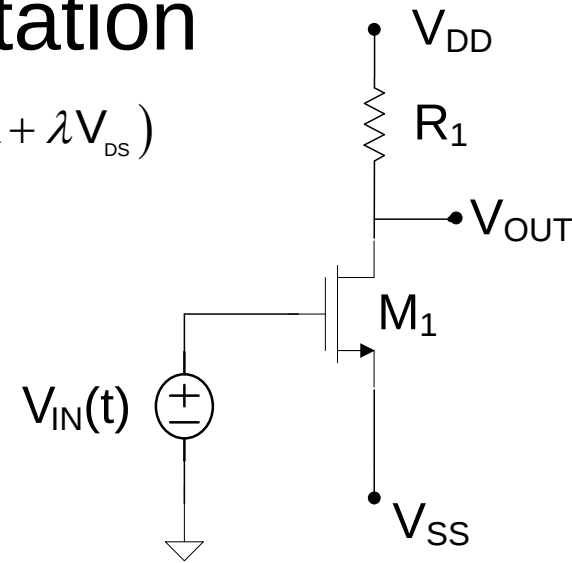
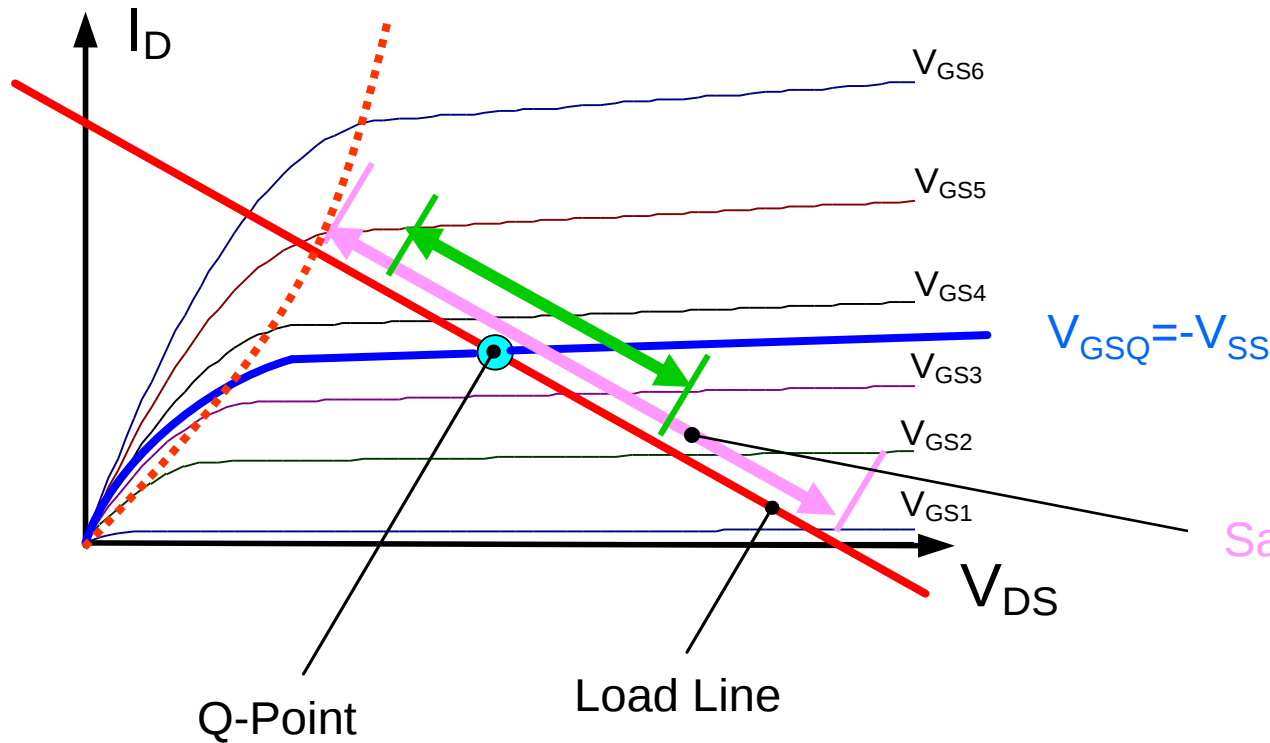


$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

As V_{IN} changes around Q-point, due to changes V_{IN} induces in V_{GS} , the operating point must remain on the load line!

Graphical Analysis and Interpretation

Device Model (family of curves)
$$I_{DQ} = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$



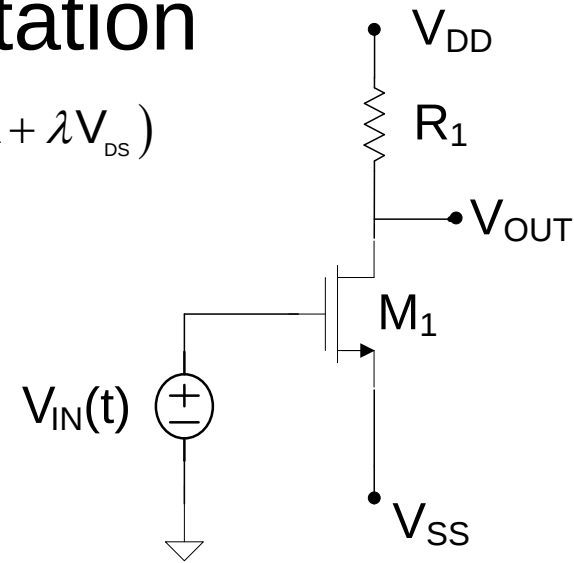
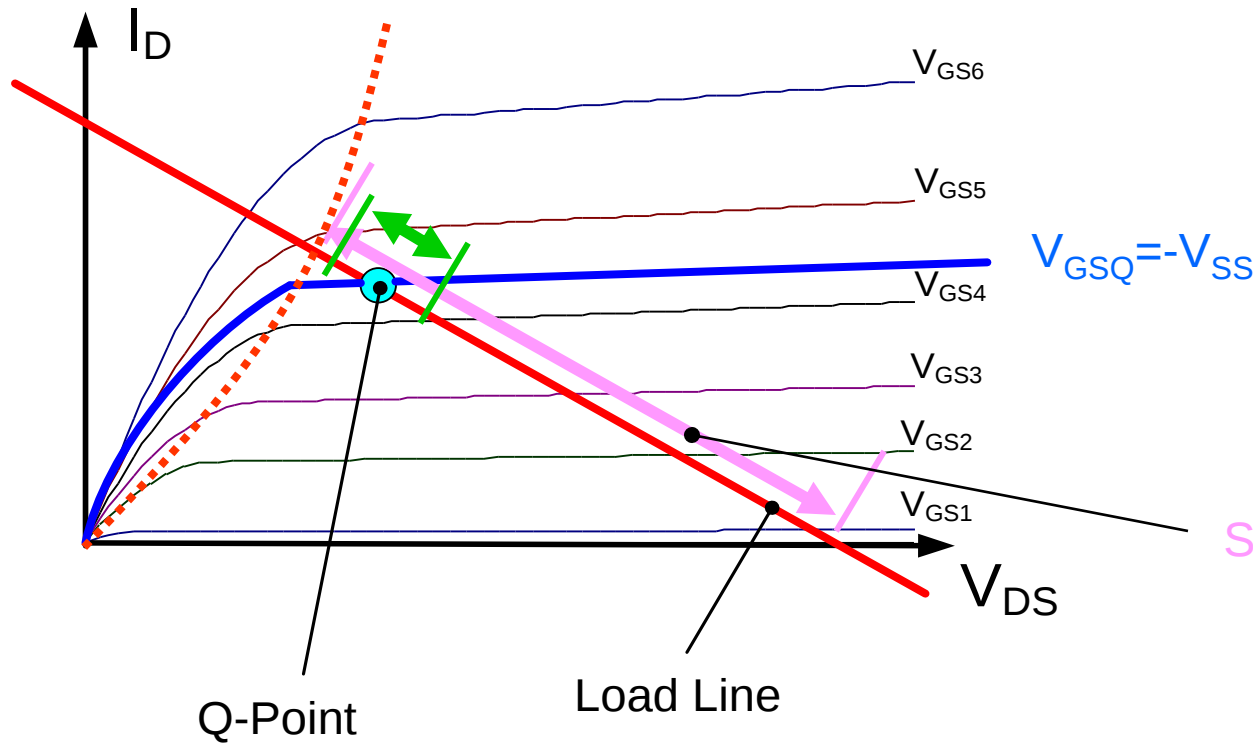
Saturation region

$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

- Linear signal swing region smaller than saturation region
- Modest nonlinear distortion provided saturation region operation maintained
- Symmetric swing about Q-point
- Signal swing can be maximized by judicious location of Q-point

Graphical Analysis and Interpretation

Device Model (family of curves)
$$I_{DQ} = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$

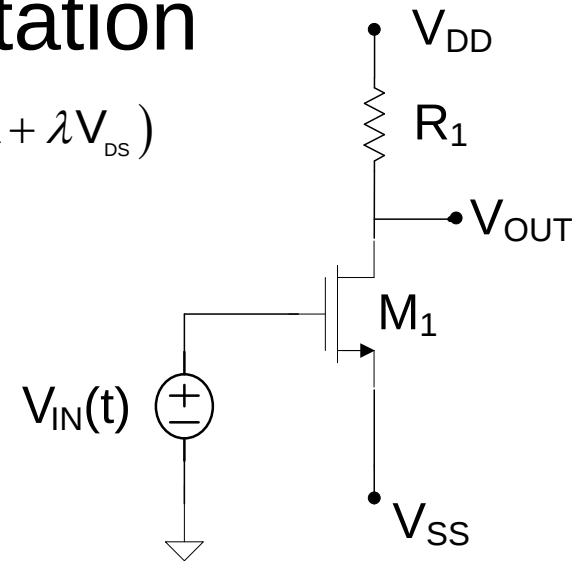
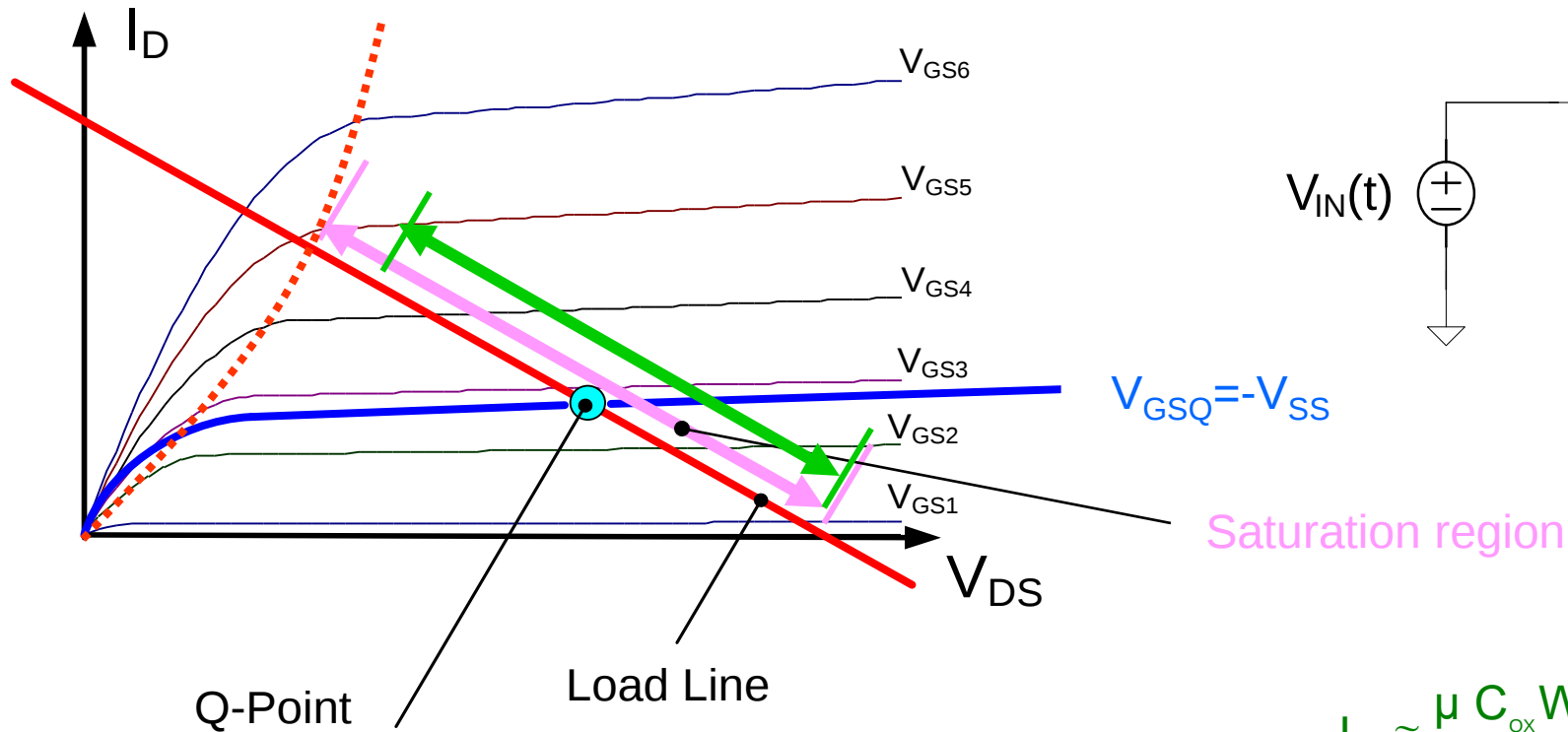


$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

Very limited signal swing with non-optimal Q-point location

Graphical Analysis and Interpretation

Device Model (family of curves) $I_{DQ} = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$



$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} (V_{SS} + V_T)^2$$

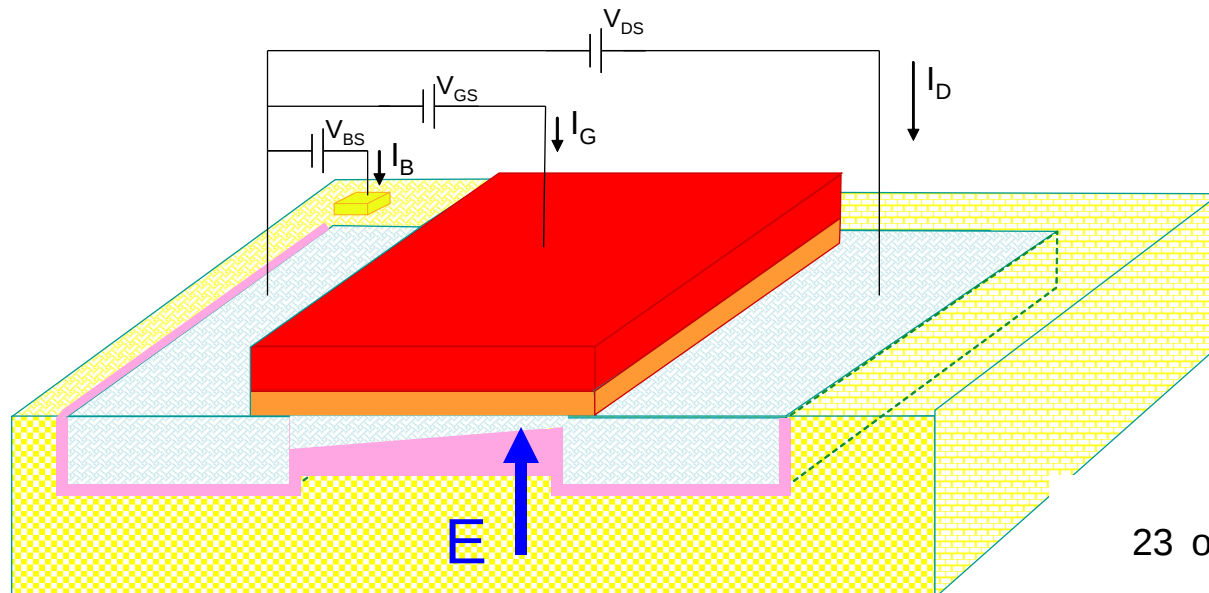
- Signal swing can be maximized by judicious location of Q-point
- Often selected to be at middle of load line in saturation region

Small-Signal MOSFET Model Extension

Existing 3-terminal small-signal model does not depend upon the bulk voltage !



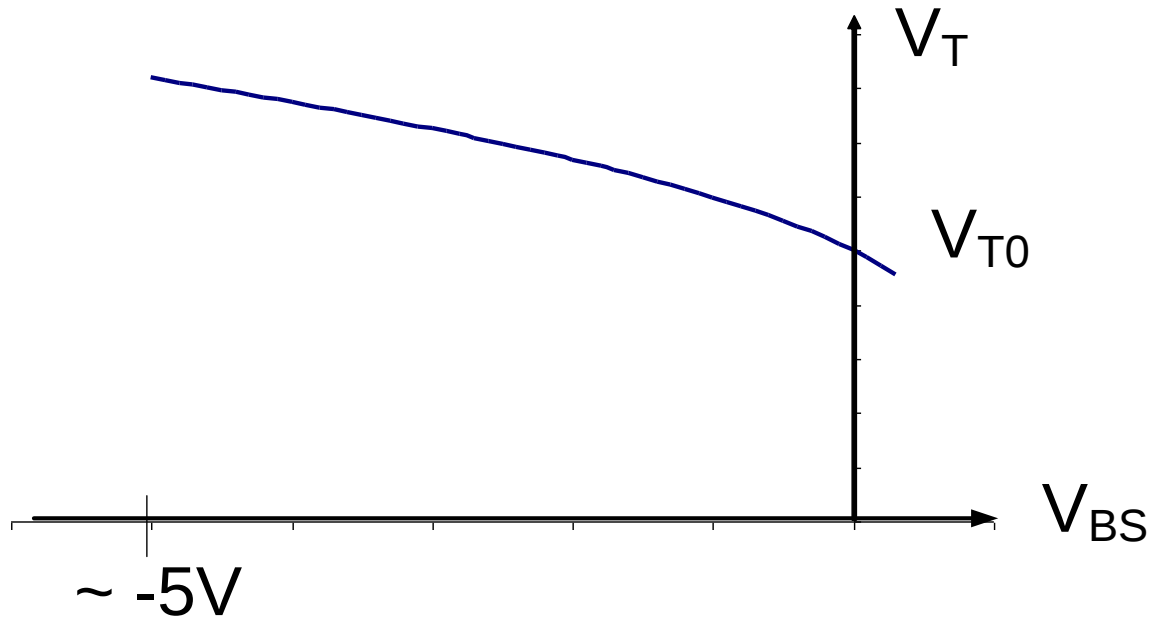
Recall that changing the bulk voltage changes the electric field in the channel region and thus the threshold voltage!



Recall: Typical Effects of Bulk on Threshold Voltage for n-channel Device

$$V_T = V_{T0} + \gamma \left[\sqrt{\phi - V_{BS}} - \sqrt{\phi} \right]$$

$$\gamma \cong 0.4V^{-\frac{1}{2}} \quad \phi \cong 0.6V$$



Bulk-Diffusion Generally Reverse Biased ($V_{BS} < 0$ or at least less than 0.3V) for n-channel

Shift in threshold voltage with bulk voltage can be substantial

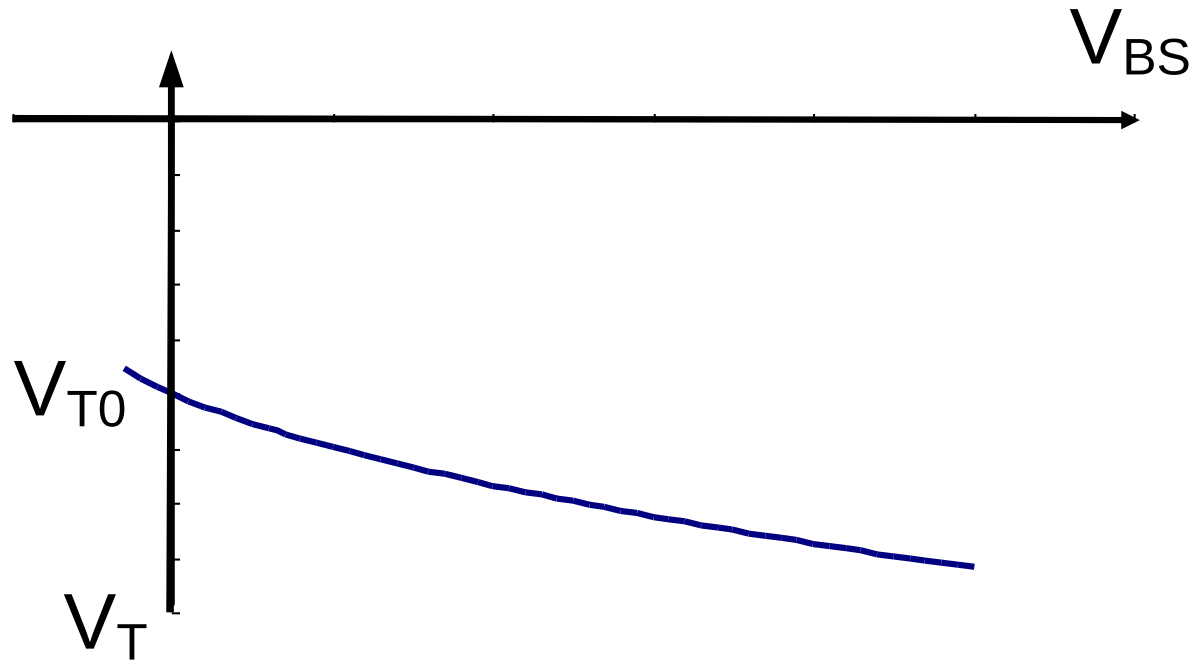
Often $V_{BS} = 0$

Recall: Typical Effects of Bulk on Threshold Voltage for p-channel Device

$$V_T = V_{T0} - \gamma \left[\sqrt{\phi + V_{BS}} - \sqrt{\phi} \right]$$

$$\gamma \cong 0.4V^{-\frac{1}{2}}$$

$$\phi \cong 0.6V$$



Bulk-Diffusion Generally Reverse Biased ($V_{BS} > 0$ or at least greater than $-0.3V$) for n-channel

Same functional form as for n-channel devices but V_{T0} is now negative and the magnitude of V_T still increases with the magnitude of the reverse bias

Recall:

4-terminal model extension

$$I_G = 0$$

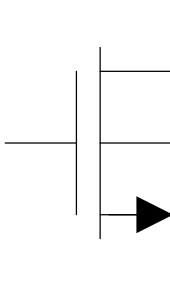
$$I_B = 0$$

$$I_D = \begin{cases} 0 & V_{GS} \leq V_T \\ \mu C_{ox} \frac{W}{L} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) V_{DS} & V_{GS} \geq V_T \quad V_{DS} < V_{GS} - V_T \\ \mu C_{ox} \frac{W}{2L} (V_{GS} - V_T)^2 \cdot (1 + \lambda V_{DS}) & V_{GS} \geq V_T \quad V_{DS} \geq V_{GS} - V_T \end{cases}$$

$$V_T = V_{T0} + \gamma \left(\sqrt{\phi - V_{BS}} - \sqrt{\phi} \right)$$

Model Parameters : $\{\mu, C_{ox}, V_{T0}, \phi, \gamma, \lambda\}$

Design Parameters : $\{W, L\}$ but only one degree of freedom W/L
biasing or quiescent point



Small-Signal 4-terminal Model Extension

$$I_G = 0$$

$$I_B = 0$$

$$I_D = \begin{cases} 0 \\ \mu C_{ox} \frac{W}{L} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) V_{DS} \end{cases}$$

$$\mu C_{ox} \frac{W}{2L} (V_{GS} - V_T)^2 \bullet (1 + \lambda V_{DS})$$

$$V_{GS} \leq V_T$$

$$V_{GS} \geq V_T \quad V_{DS} < V_{GS} - V_T$$

$$V_{GS} \geq V_T \quad V_{DS} \geq V_{GS} - V_T$$

$$V_T = V_{T0} + \gamma \left(\sqrt{\phi - V_{BS}} - \sqrt{\phi} \right)$$

$$y_{11} = \left. \frac{\partial I_G}{\partial V_{GS}} \right|_{\bar{V}=\bar{V}_Q} = 0 \quad y_{12} = \left. \frac{\partial I_G}{\partial V_{DS}} \right|_{\bar{V}=\bar{V}_Q} = 0 \quad y_{13} = \left. \frac{\partial I_G}{\partial V_{BS}} \right|_{\bar{V}=\bar{V}_Q} = 0$$

$$y_{21} = \left. \frac{\partial I_D}{\partial V_{GS}} \right|_{\bar{V}=\bar{V}_Q} = g_m \quad y_{22} = \left. \frac{\partial I_D}{\partial V_{DS}} \right|_{\bar{V}=\bar{V}_Q} = g_o \quad y_{23} = \left. \frac{\partial I_D}{\partial V_{BS}} \right|_{\bar{V}=\bar{V}_Q} = g_{mb}$$

$$y_{31} = \left. \frac{\partial I_B}{\partial V_{GS}} \right|_{\bar{V}=\bar{V}_Q} = 0 \quad y_{32} = \left. \frac{\partial I_B}{\partial V_{DS}} \right|_{\bar{V}=\bar{V}_Q} = 0 \quad y_{33} = \left. \frac{\partial I_B}{\partial V_{BS}} \right|_{\bar{V}=\bar{V}_Q} = 0$$

Small-Signal 4-terminal Model Extension

$$I_D = \mu C_{ox} \frac{W}{2L} (V_{GS} - V_T)^2 \cdot (1 + \lambda V_{DS})$$

Definition:

$$V_{EB} = V_{GS} - V_T$$

$$V_{EBQ} = V_{GSQ} - V_{TQ}$$

$$V_T = V_{T0} + \gamma \left(\sqrt{\phi - V_{BS}} - \sqrt{\phi} \right)$$

$$g_m = \left. \frac{\partial I_D}{\partial V_{GS}} \right|_{\vec{V}=\vec{V}_Q} = \mu C_{ox} \frac{W}{2L} 2(V_{GS} - V_T)^1 \cdot (1 + \lambda V_{DS}) \Big|_{\vec{V}=\vec{V}_Q} \cong \mu C_{ox} \frac{W}{L} V_{EBQ}$$

Same as 3-term

$$g_o = \left. \frac{\partial I_D}{\partial V_{DS}} \right|_{\vec{V}=\vec{V}_Q} = \mu C_{ox} \frac{W}{2L} 2(V_{GS} - V_T)^2 \cdot \lambda \Big|_{\vec{V}=\vec{V}_Q} \cong \lambda I_{DQ}$$

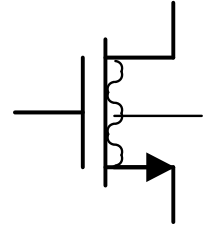
Same as 3-term

$$g_{mb} = \left. \frac{\partial I_D}{\partial V_{BS}} \right|_{\vec{V}=\vec{V}_Q} = \mu C_{ox} \frac{W}{2L} 2(V_{GS} - V_T)^1 \cdot \left(-\frac{\partial V_T}{\partial V_{BS}} \right) \cdot (1 + \lambda V_{DS}) \Big|_{\vec{V}=\vec{V}_Q}$$

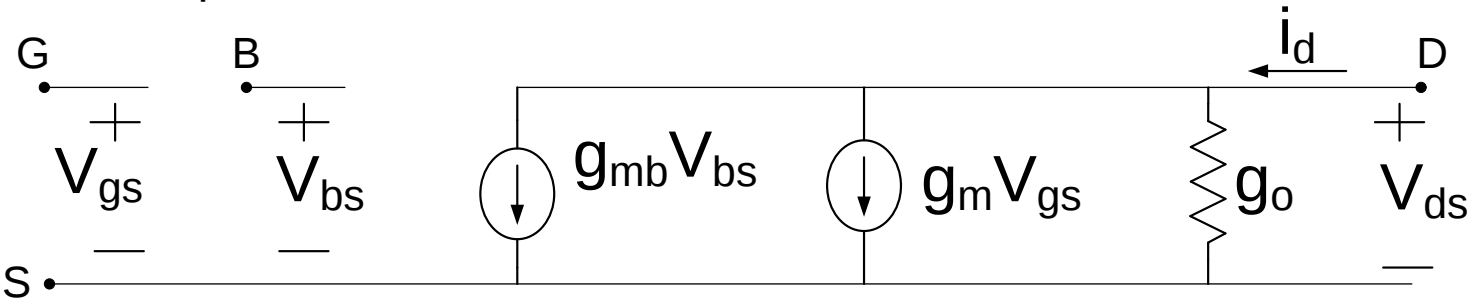
$$g_{mb} = \left. \frac{\partial I_D}{\partial V_{BS}} \right|_{\vec{V}=\vec{V}_Q} \cong \mu C_{ox} \frac{W}{L} V_{EBQ} \cdot \left. \frac{\partial V_T}{\partial V_{BS}} \right|_{\vec{V}=\vec{V}_Q} = \left(\mu C_{ox} \frac{W}{L} V_{EBQ} \right) (-1) \gamma \frac{1}{2} (\phi - V_{BS})^{-\frac{1}{2}} \Big|_{\vec{V}=\vec{V}_Q} (-1)$$

$$g_{mb} \cong g_m \frac{\gamma}{2\sqrt{\phi - V_{BSQ}}}$$

Small Signal MOSFET Equivalent Circuit



An equivalent Circuit:



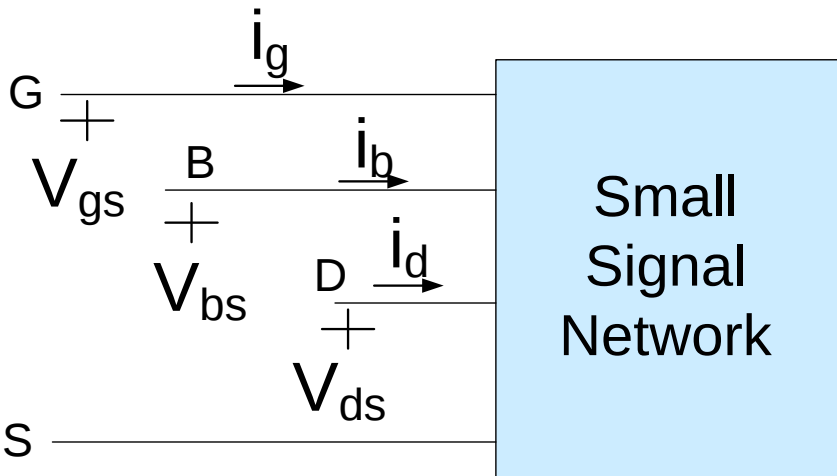
$$g_m = \frac{\mu C_{ox} W}{L} (V_{GSQ} - V_T)$$

$$g_o = \lambda I_{DQ}$$

$$g_{mb} = g_m \left(\frac{\gamma}{2\sqrt{\phi - V_{BSQ}}} \right)$$

This contains absolutely no more information than the set of small-signal model equations

Small Signal 4-terminal MOSFET Model Summary



$$i_g = 0$$

$$i_b = 0$$

$$i_d = g_m v_{gs} + g_{mb} v_{bs} + g_o v_{ds}$$

$$g_m = \frac{\mu C_{ox} W}{L} v_{EBQ}$$

$$g_o = \lambda I_{DQ}$$

$$g_{mb} = g_m \left(\frac{\gamma}{2\sqrt{\phi - V_{bsQ}}} \right)$$

Relative Magnitude of Small Signal MOS Parameters

Consider:

$$i_d = g_m v_{gs} + g_{mb} v_{bs} + g_o v_{ds}$$

3 alternate equivalent expressions for g_m

$$g_m = \frac{\mu C_{ox} W}{L} V_{EBQ} \quad g_m = \sqrt{\frac{2\mu C_{ox} W}{L}} \sqrt{I_{DQ}} \quad g_m = \frac{2I_{DQ}}{V_{EBQ}}$$

Consider, as an example:

$$\mu C_{ox} = 100 \mu A/V^2, \lambda = .01 V^{-1}, \gamma = 0.4 V^{0.5}, V_{EBQ} = 1V, W/L = 1, V_{BSQ} = 0V$$

$$I_{DQ} \cong \frac{\mu C_{ox} W}{2L} V_{EBQ}^2 = \frac{10^{-4} W}{2L} (1V)^2 = 5E-5$$

$$g_m = \frac{\mu C_{ox} W}{L} V_{EBQ} = 1E-4$$

$$g_o = \lambda I_{DQ} = 5E-7$$

$$g_{mb} = g_m \left(\frac{\gamma}{2\sqrt{\phi - V_{BSQ}}} \right) = .26g_m$$

In this example

$$g_o \ll g_m, g_{mb}$$

$$g_{mb} < g_m$$

This relationship is common

In many circuits, $V_{BS} = 0$ as well

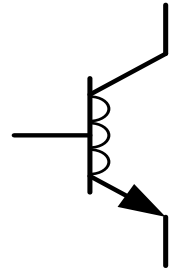
- Often the g_o term can be neglected in the small signal model because it is so small
- Be careful about neglecting g_o prior to obtaining a final expression

Relative Magnitude of Small Signal BJT Parameters

$$g_m = \frac{I_{CQ}}{V_t}$$

$$g_\pi = \frac{I_{CQ}}{\beta V_t}$$

$$g_o \cong \frac{I_{CQ}}{V_{AF}}$$



$$\frac{g_m}{g_\pi} = \frac{\left[\frac{I_Q}{V_t} \right]}{\left[\frac{I_Q}{\beta V_t} \right]}$$

for vertical npn

$$g_m \gg g_\pi \gg g_o$$

$$\frac{g_\pi}{g_o} = \frac{\left[\frac{I_Q}{\beta V_t} \right]}{\left[\frac{I_Q}{V_{AF}} \right]}$$

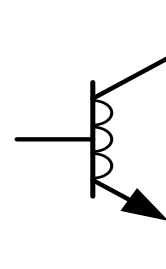
Often the g_o term can be neglected in the small signal model because it is so small

Relative Magnitude of Small Signal BJT Parameters

$$g_m = \frac{I_{CQ}}{V_t}$$

$$g_{\pi} = \frac{I_{CQ}}{\beta V_t}$$

$$g_o \cong \frac{I_{CQ}}{V_{AF}}$$



for vertical npn

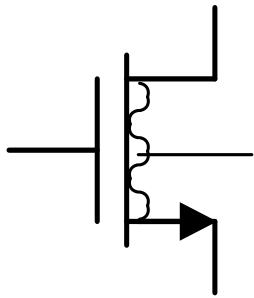
$$g_m \gg g_{\pi} \gg g_o$$

$$\frac{g_m}{g_{\pi}} = \frac{\left[\frac{I_Q}{V_t} \right]}{\left[\frac{I_Q}{\beta V_t} \right]} = \beta$$

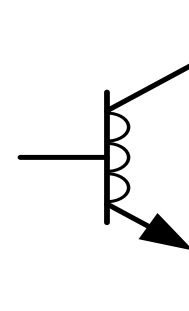
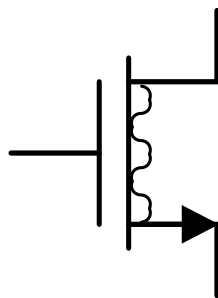
$$\frac{g_{\pi}}{g_o} = \frac{\left[\frac{I_Q}{\beta V_t} \right]}{\left[\frac{I_Q}{V_{AF}} \right]} = \frac{V_{AF}}{\beta V_t} \approx \frac{200V}{100 \cdot 26mV} = 77$$

- Often the g_o term can be neglected in the small signal model because it is so small
- **Be careful about neglecting g_o prior to obtaining a final expression**

Small Signal Model Simplifications for the MOSFET and BJT



MOSFET

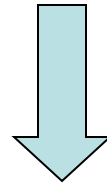
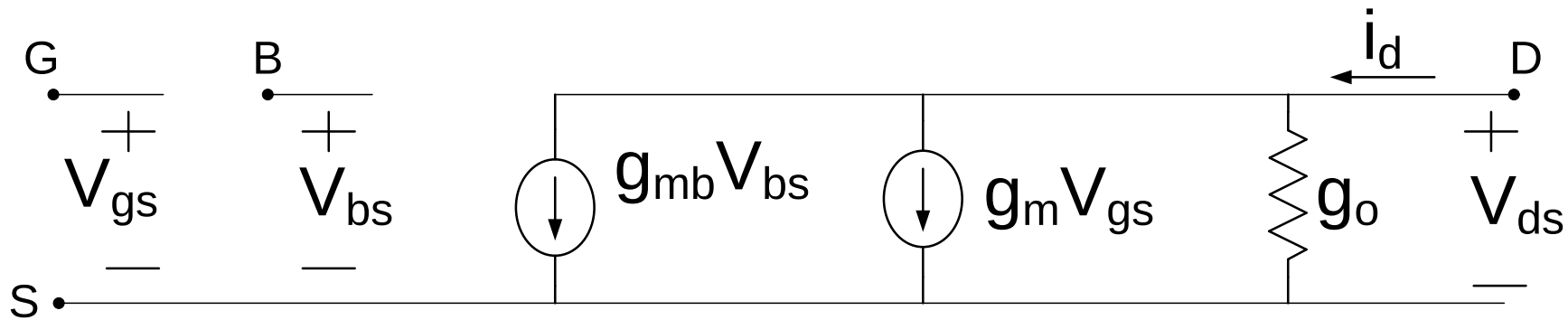


BJT

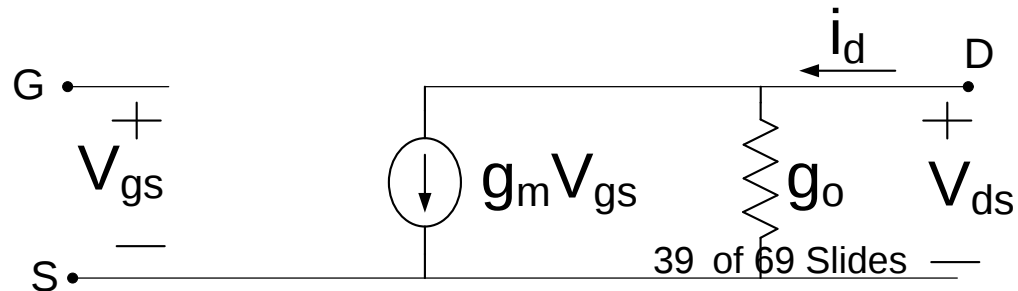
Often simplifications of the small signal model are adequate for a given application

These simplifications will be discussed next

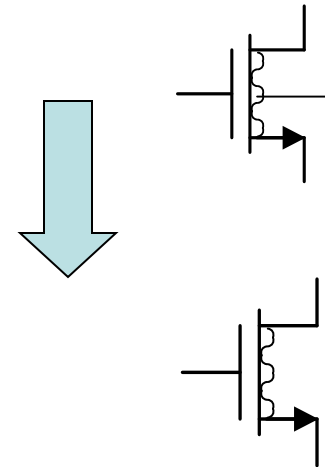
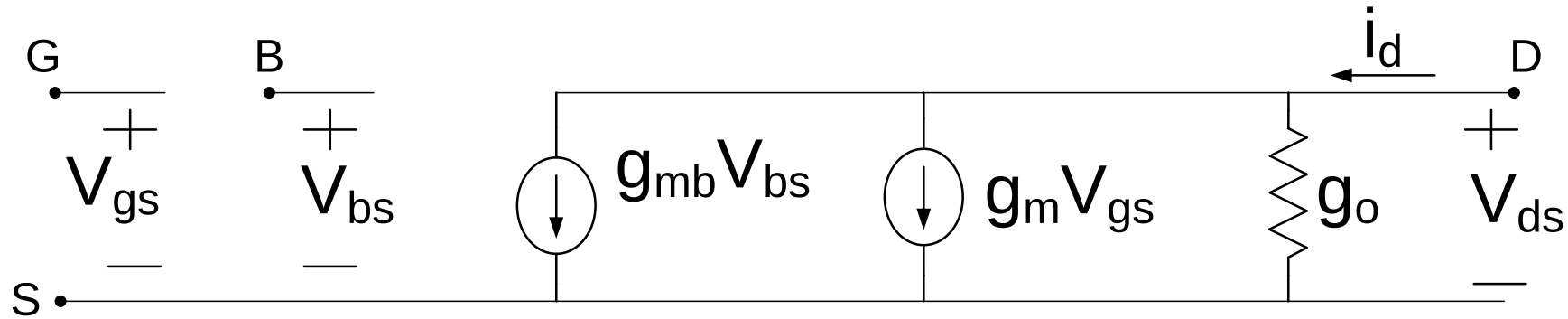
Small Signal Model Simplifications



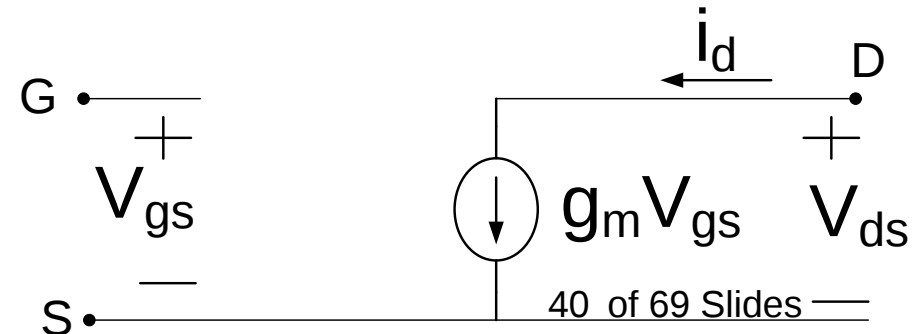
Simplification that is often adequate



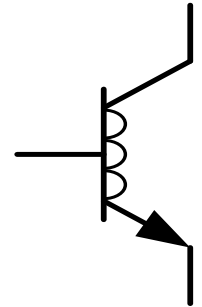
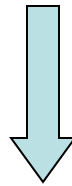
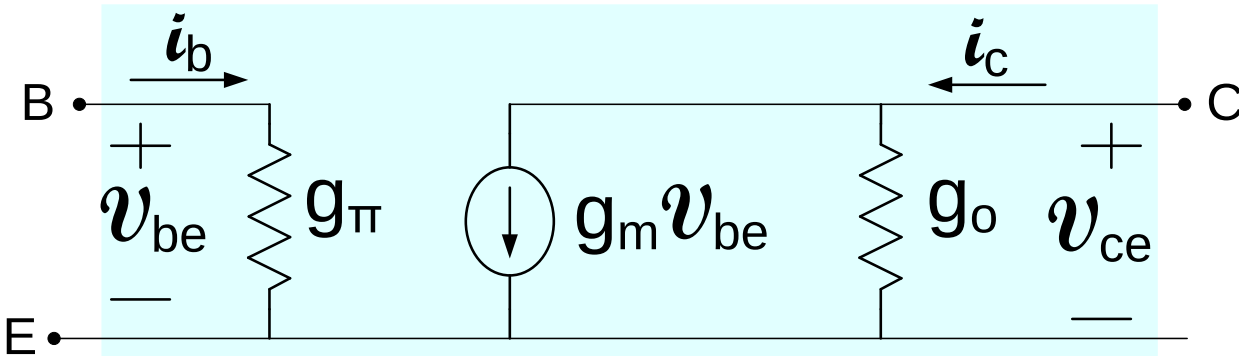
Small Signal Model Simplifications



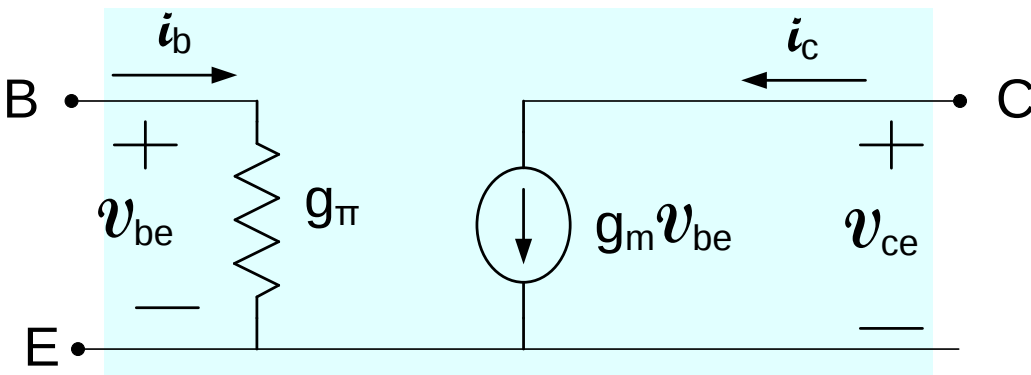
Even further simplification that is often adequate



Small Signal BJT Model Simplifications

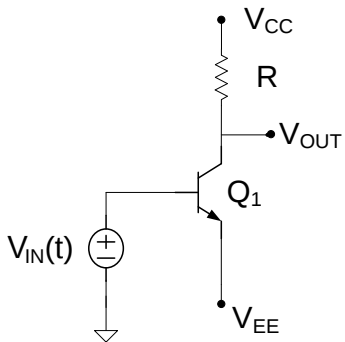


Simplification that is often adequate



Large and Small Signal Parameter Domains

BJT



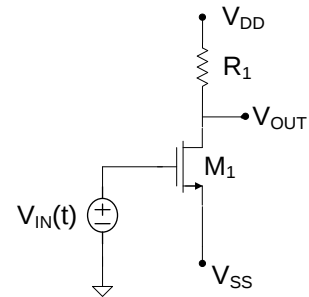
$$A_{VB} = -\frac{I_{CQ} R_1}{V_t}$$

$$A_V = -g_m R$$

$$A_{VM} = \frac{2I_{DQ} R}{[V_{SS} + V_T]}$$

$$A_V = -g_m R$$

MOSFET



Large Signal Parameter Domain: Quiescent Port and Model Variables

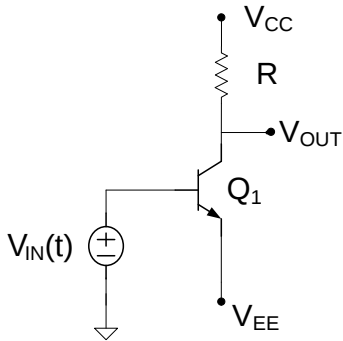
(No small-signal model parameters or small-signal port variables)

Small Signal Parameter Domain: Small-Signal Port and Model Variables

(No dc model parameters or dc port variables)

Gains for MOSFET and BJT Circuits

BJT

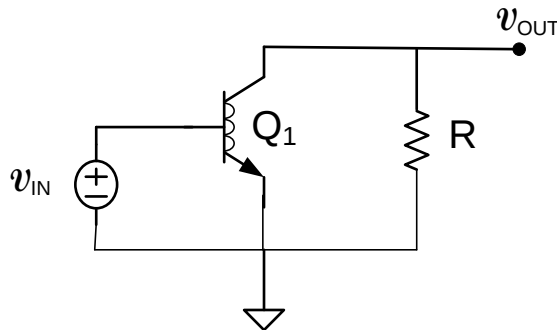


$$A_{VB} = -\frac{I_{CQ} R_1}{V_t}$$

Large Signal Parameter Domain
(If g_o is neglected)

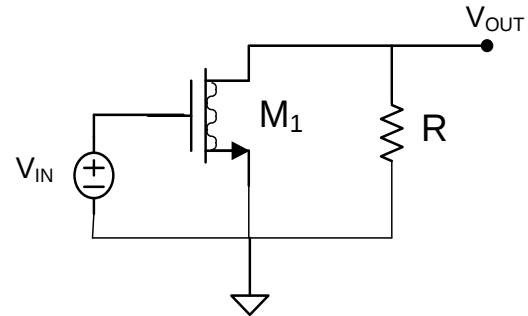
$$A_{VM} = \frac{2I_{DQ} R}{[V_{SS} + V_T]}$$

For both circuits

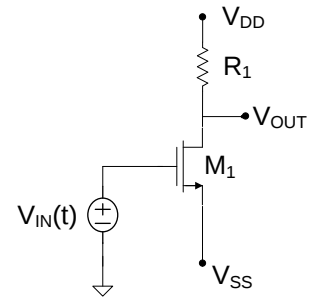


Small Signal Parameter Domain
(neglecting g_o)

$$A_v = -g_m R$$

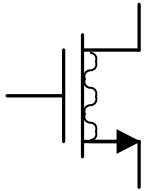


MOSFET



- Gains are identical in small-signal parameter domain !
- Gains vary linearly with small signal parameter g_m
- Power is often a key resource in the design of an integrated circuit
- In both circuits, power is proportional to I_{CQ} , I_{DQ} (if V_{SS} and V_{EE} are fixed)

How does g_m vary with I_{DQ} ?



$$g_m = \sqrt{\frac{2\mu C_{ox} W}{L}} \sqrt{I_{DQ}}$$

Varies with the square root of I_{DQ}

$$g_m = \frac{2I_{DQ}}{V_{GSQ} - V_T} = \frac{2I_{DQ}}{V_{EBQ}}$$

Varies linearly with I_{DQ}

$$g_m = \frac{\mu C_{ox} W}{L} (V_{GSQ} - V_T)$$

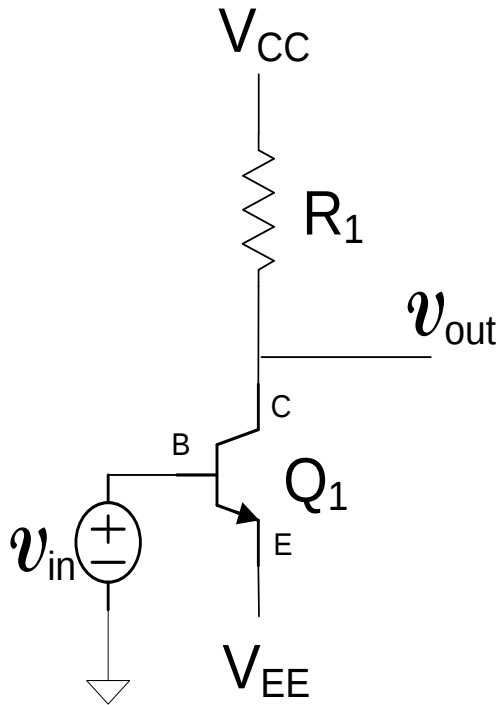
Doesn't vary with I_{DQ}

How does g_m vary with I_{DQ} ?

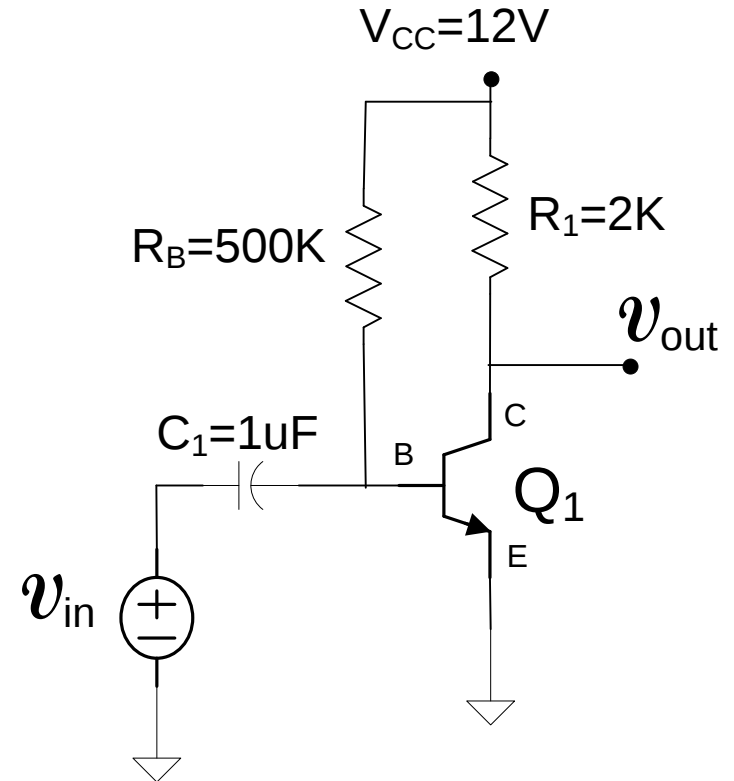
All of the above are true – but with qualification

g_m is a function of more than one variable (I_{DQ}) and how it varies depends upon how the remaining variables are constrained

Amplifier Biasing (precursor)



Not convenient to have multiple dc power supplies
 V_{OUTQ} very sensitive to V_{EE}

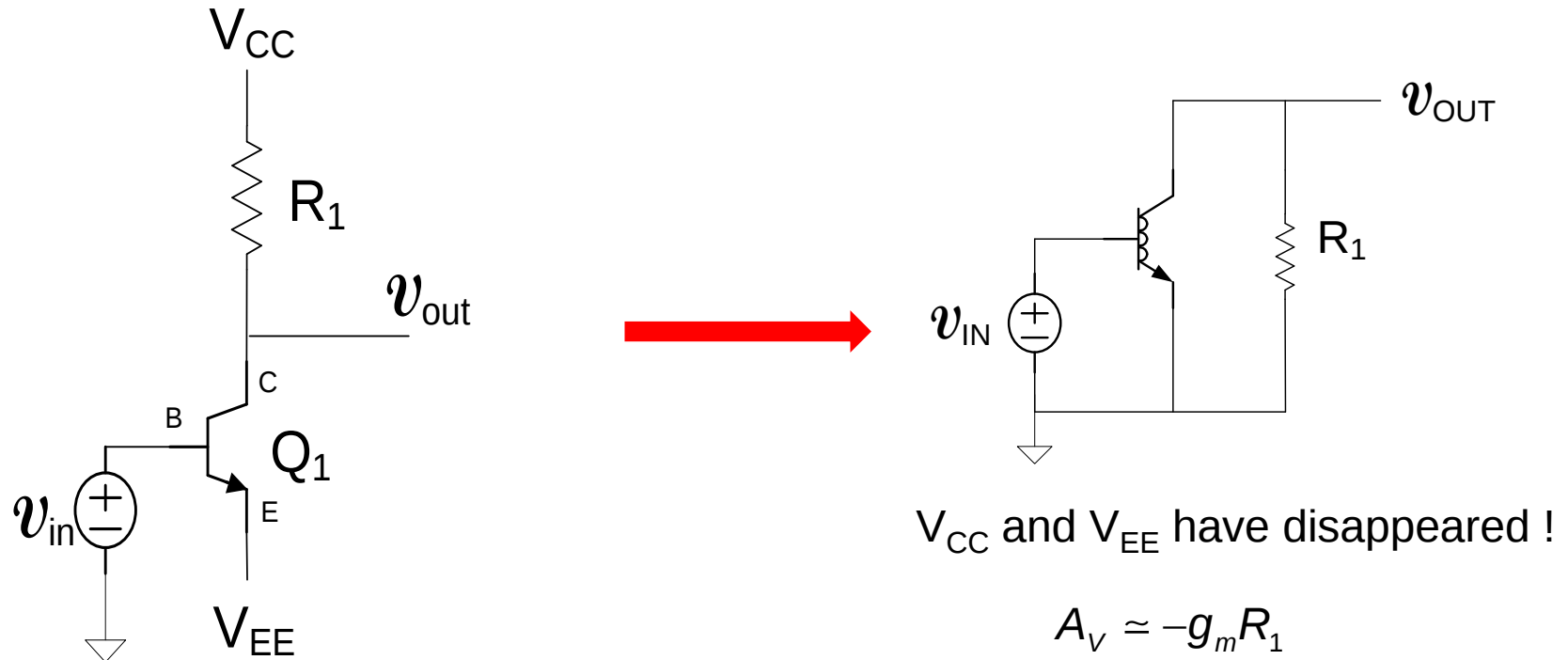


Single power supply
Additional resistor and capacitor

Compare the small-signal equivalent circuits of these two structures

Compare the small-signal voltage gain of these two structures

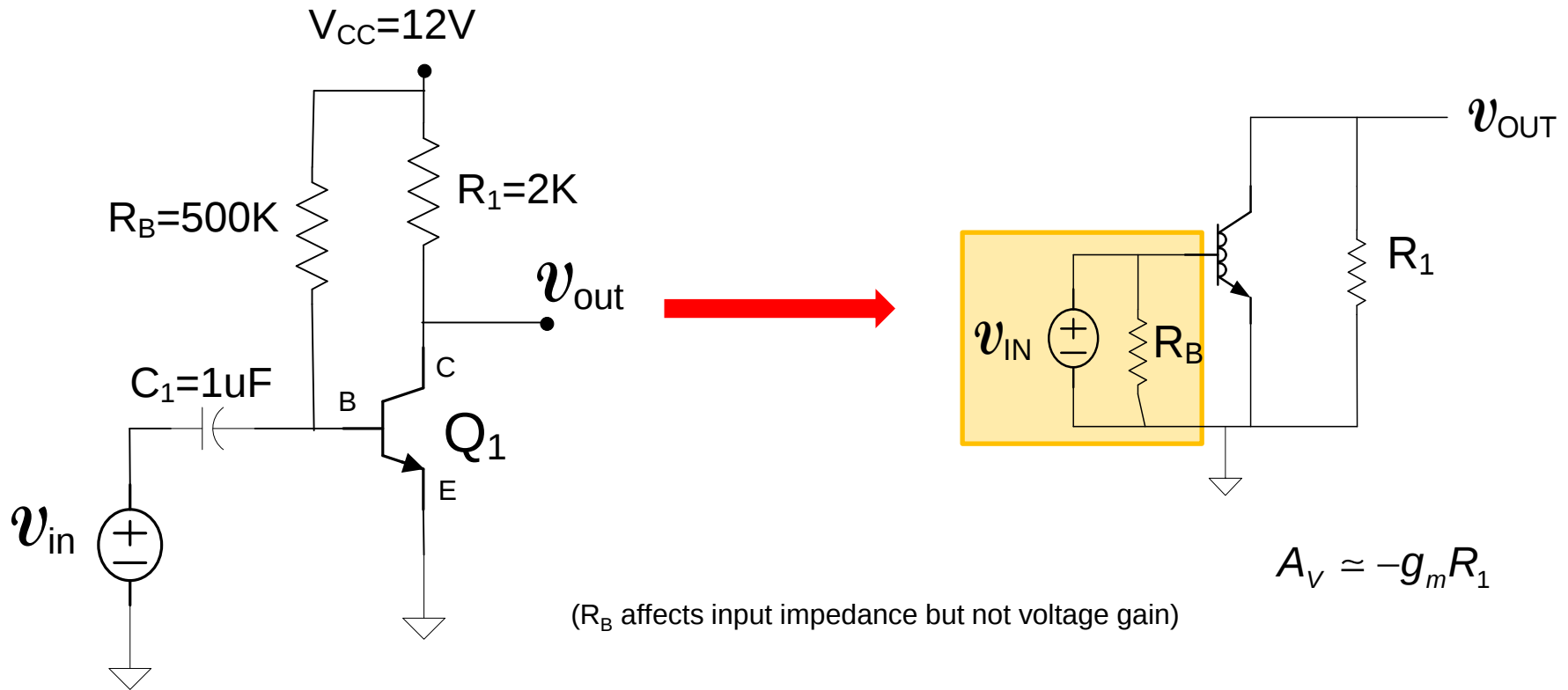
Amplifier Biasing (precursor)



- Voltage sources V_{EE} and V_{CC} used for biasing
- Not convenient to have multiple dc power supplies
- V_{OUTQ} very sensitive to V_{EE}

- Biasing is used to obtain the desired operating point of a circuit
- Ideally the biasing circuit should not distract significantly from the basic operation of the circuit

Amplifier Biasing (precursor)



Single power supply

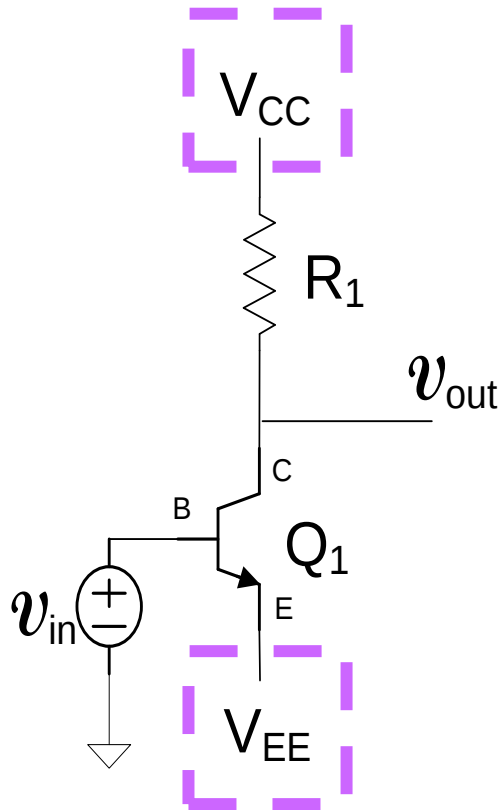
Additional resistor and capacitor

Thevenin Equivalent of v_{IN} & R_B is v_{IN}

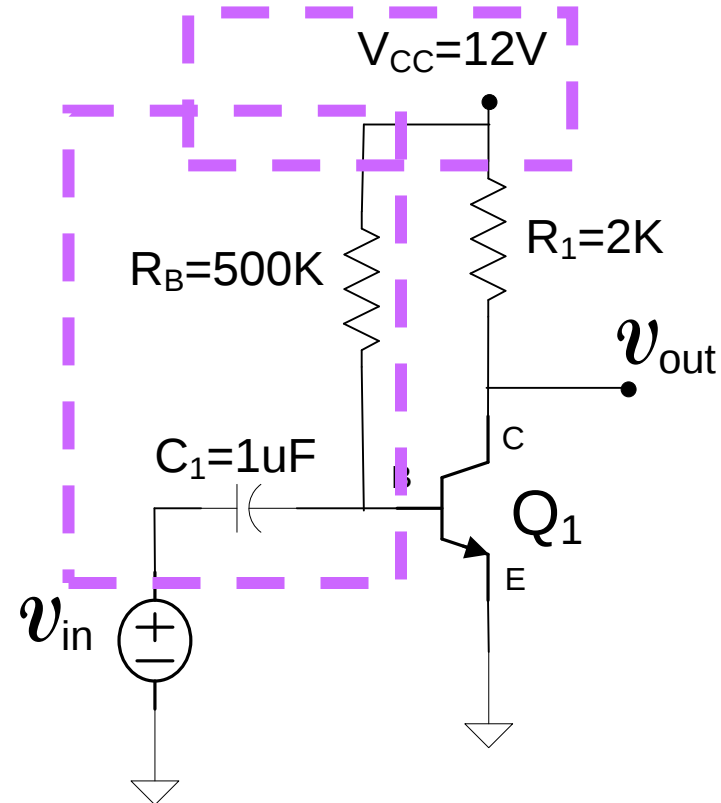
- Biasing is used to obtain the desired operating point of a circuit
- Ideally the biasing circuit should not distract significantly from the basic operation of the circuit

Amplifier Biasing (precursor)

Biassing Circuits shown in purple

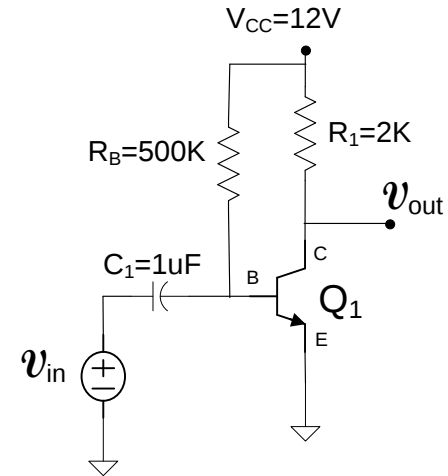
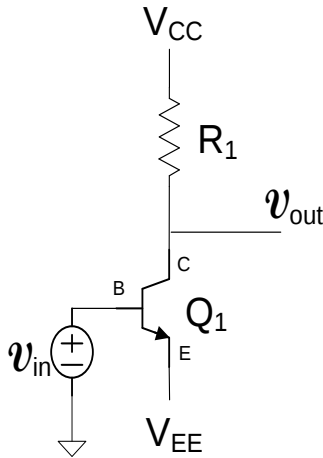


Not convenient to have multiple dc power supplies
 V_{OUTQ} very sensitive to V_{EE}

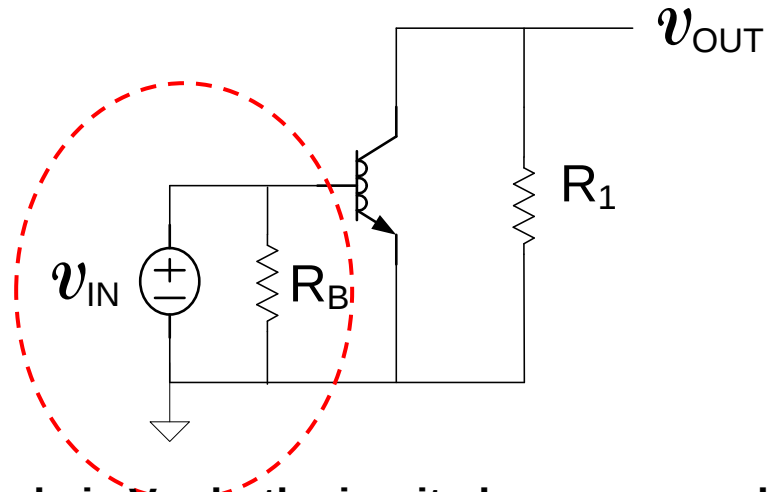
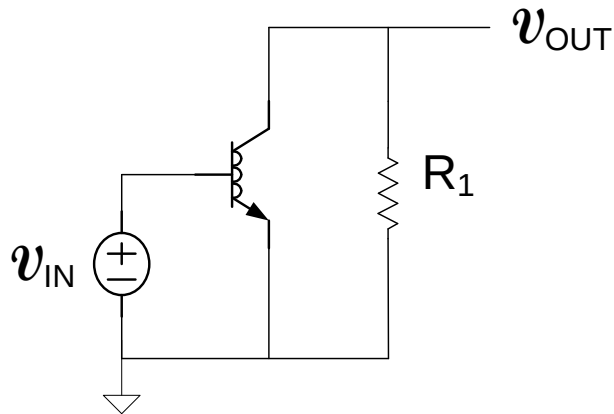


Single power supply
Additional resistor and capacitor

Amplifier Biasing (precursor)



Compare the small-signal equivalent circuits of these two structures



Since Thevenin equivalent circuit in red circle is V_{IN} , both circuits have same voltage gain

But the load placed on V_{IN} is different

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Method of characterizing the amplifiers is needed to assess impact of difference

- Small-Signal Analysis
 - Graphical Interpretation
 - MOSFET Model Extensions
 - Biasing (a precursor)

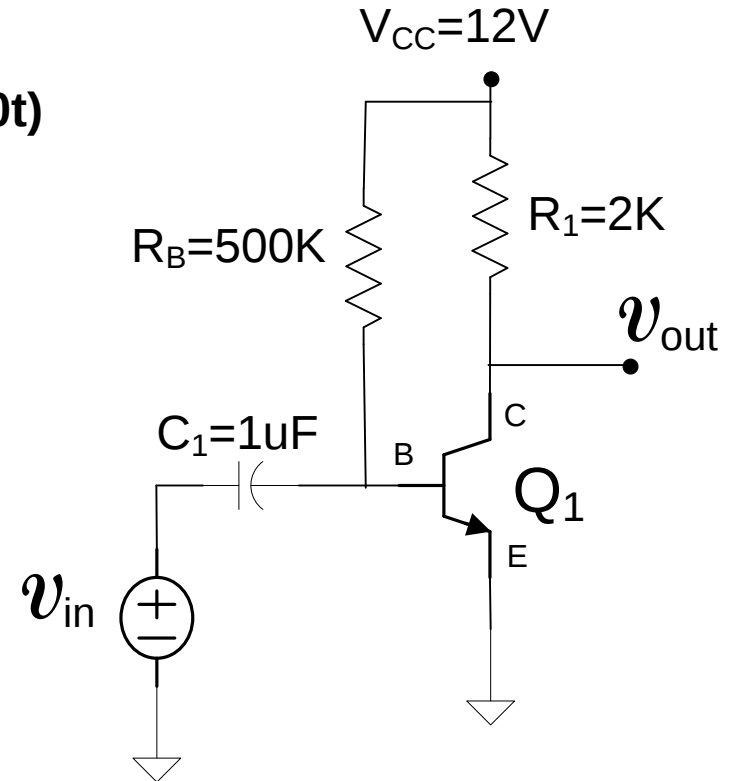
 Two-Port Amplifier Modeling

Amplifier Characterization (an example)

This example serves as a precursor to amplifier characterization

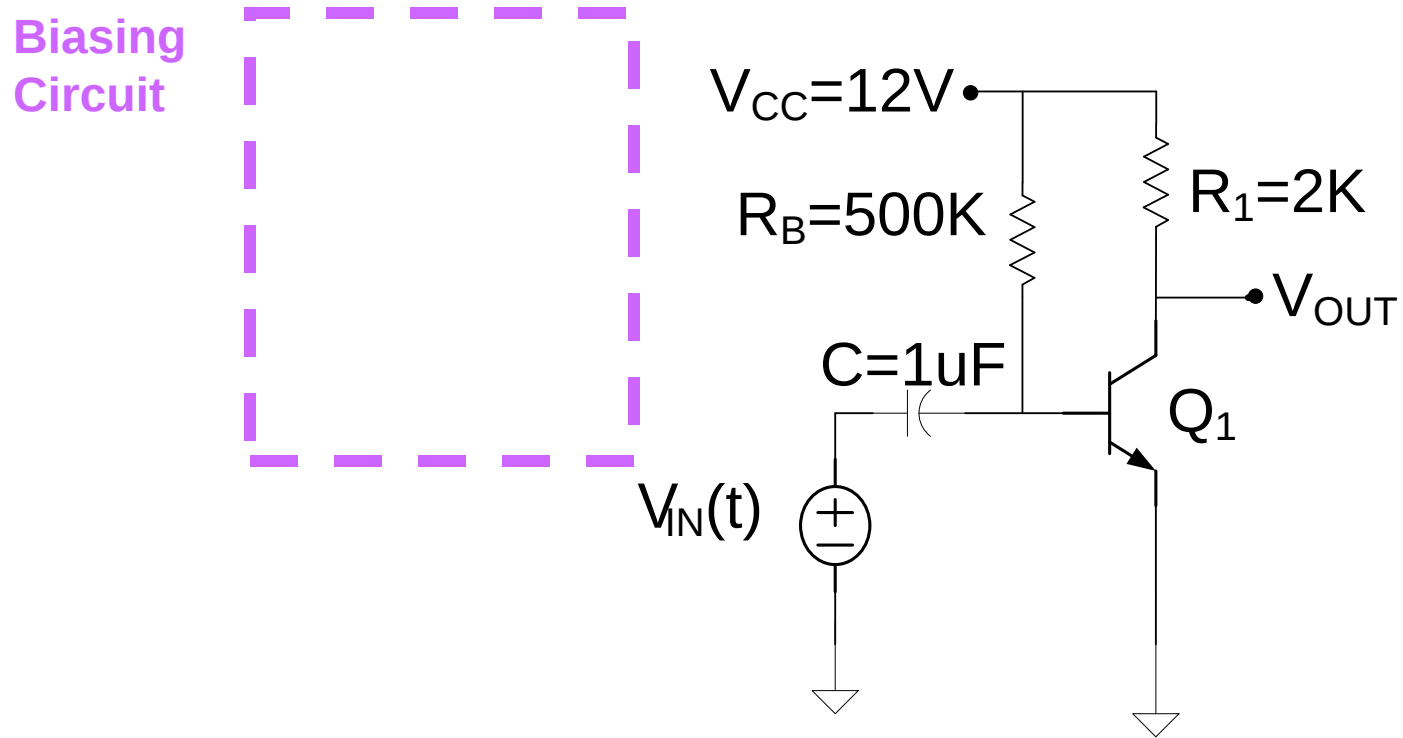
Determine V_{OUTQ} , A_v , R_{IN} Assume $\beta=100$

Determine v_{OUT} and $V_{OUT}(t)$ if $v_{IN}=.002\sin(400t)$



In the following slides we will analyze this circuit

Amplifier Characterization (an example)



(biasing components: C , R_B , V_{CC} in this case, all disappear in small-signal gain circuit)

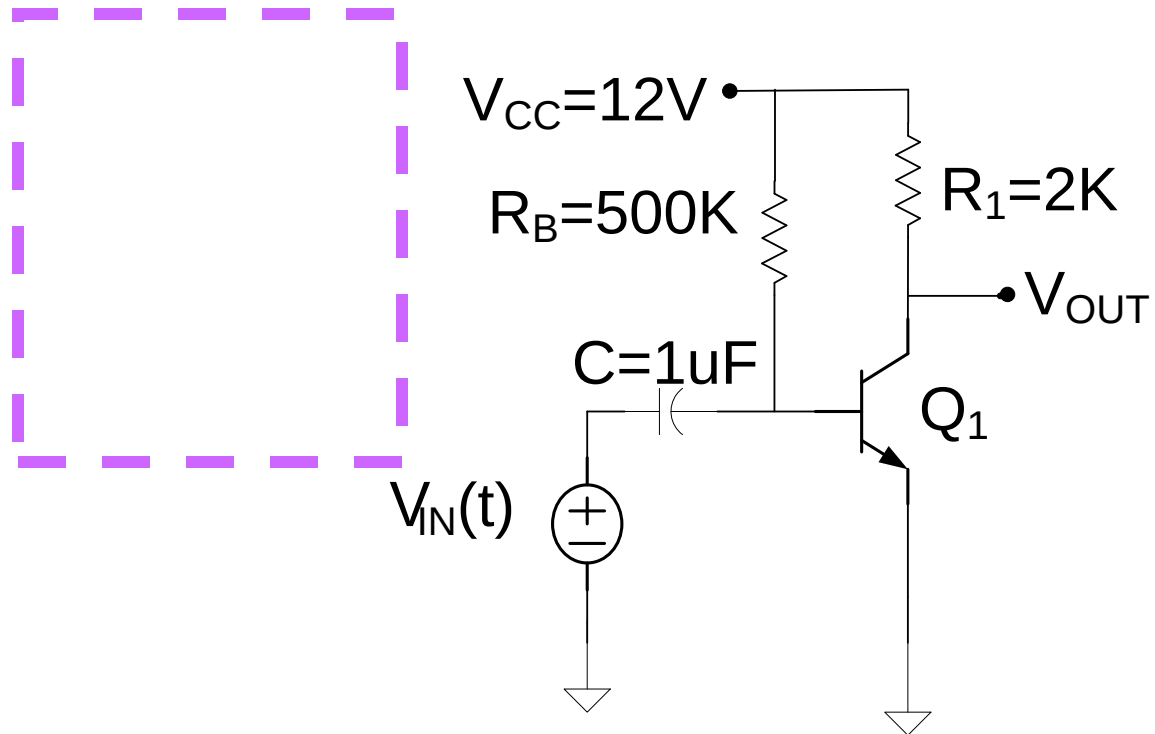
Several different biasing circuits can be used

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Amplifier Characterization (an example)

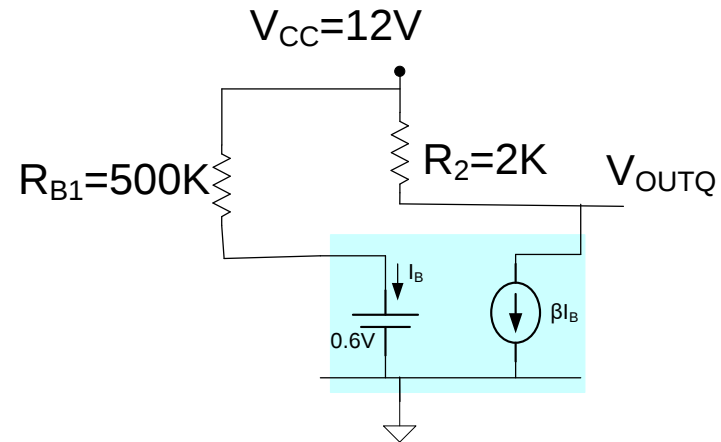
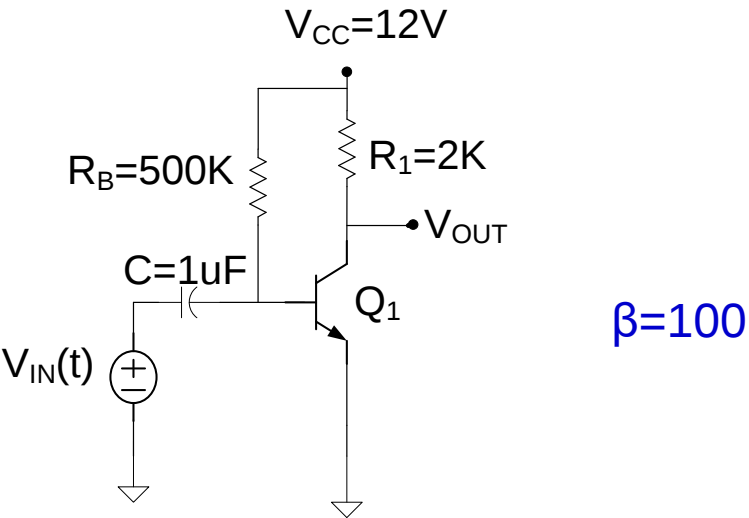
Determine V_{OUTQ} , A_V , R_{IN}

Biased
Circuit



Amplifier Characterization (an example)

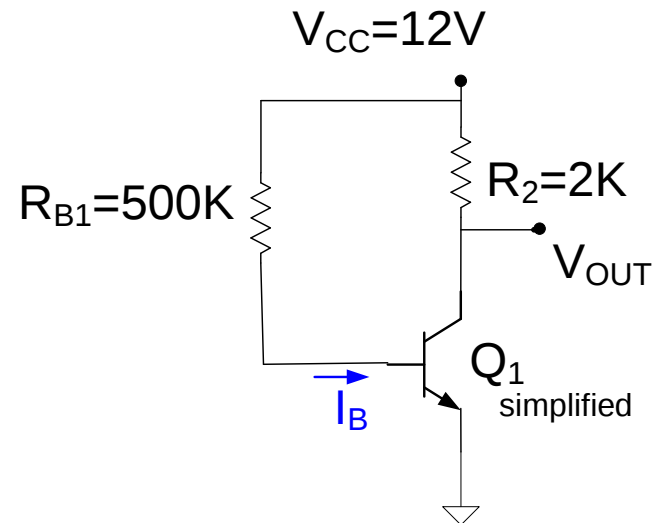
Determine V_{OUTQ}



dc equivalent circuit

$$I_{CQ} = \beta I_{BQ} = 100 \left(\frac{12V - 0.6V}{500K} \right) = 2.3mA$$

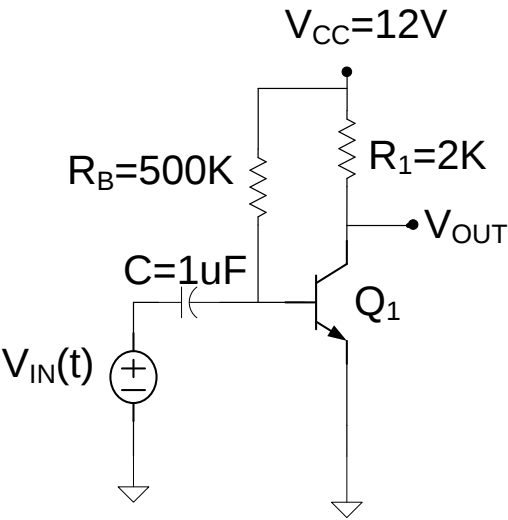
$$V_{OUTQ} = 12V - I_{CQ} R_1 = 12V - 2.3mA \cdot 2K = 7.4V$$



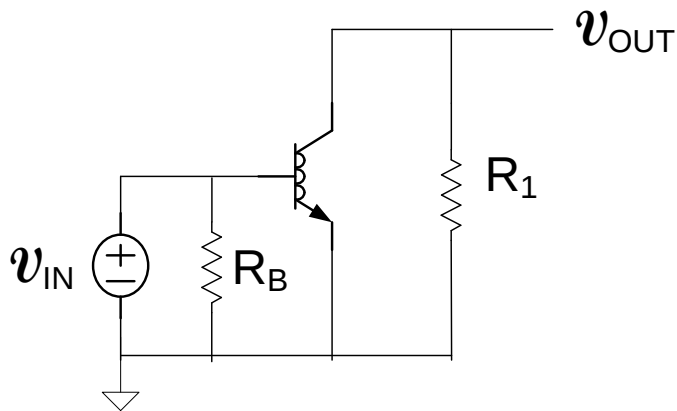
dc equivalent circuit

Amplifier Characterization (an example)

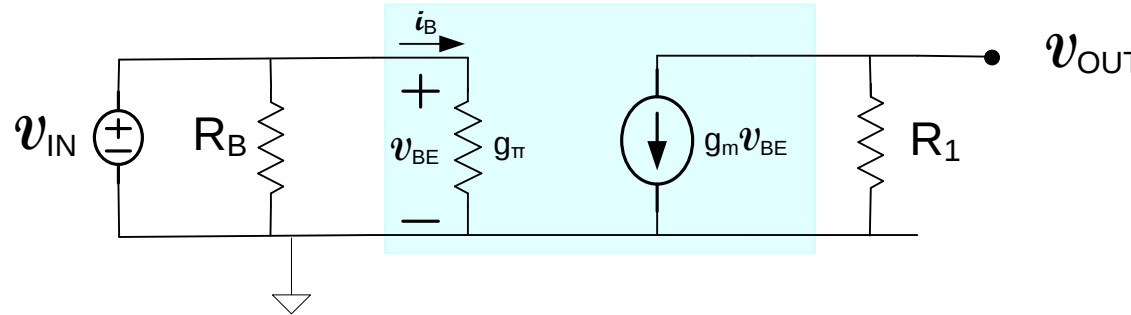
Determine the SS voltage gain (A_V)



$\beta=100$



ss equivalent circuit



ss equivalent circuit

$$\left. \begin{aligned} v_{OUT} &= -g_m v_{BE} R_1 \\ v_{IN} &= v_{BE} \end{aligned} \right\}$$

$$A_V = -R_1 g_m$$

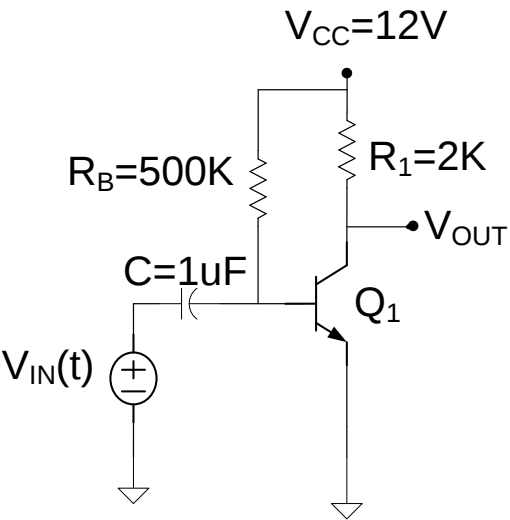
$$A_V \cong -\frac{I_{CQ} R_1}{V_t}$$

$$A_V \cong -\frac{2.3\text{mA} \cdot 2\text{K}}{26\text{mV}} \cong -177$$

This basic amplifier structure is widely used and repeated analysis serves no useful purpose

Have seen this circuit before but will repeat for review purposes

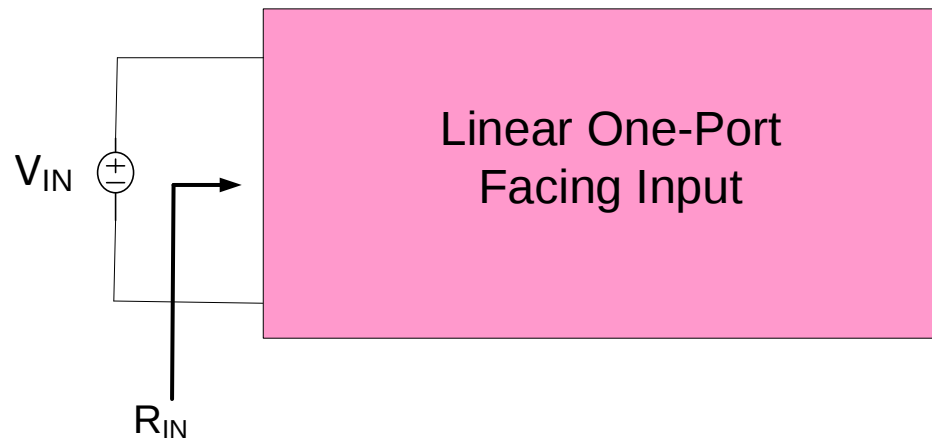
Amplifier Characterization (an example)



$\beta=100$

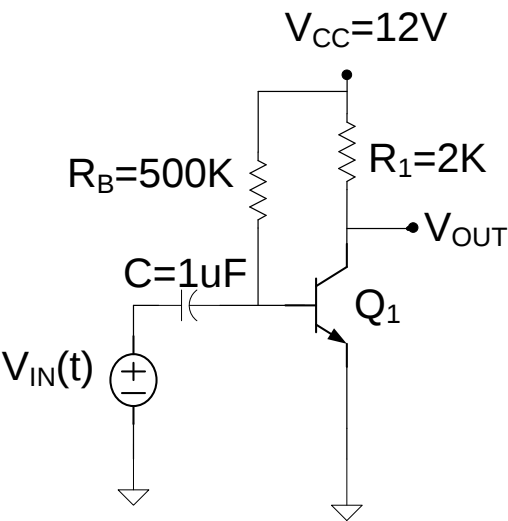
Determine V_{OUTQ} , A_V , R_{IN} ✓

- Here R_{IN} is defined to be the impedance facing V_{IN}
- Here any load is assumed to be absorbed into the one-port
- Later will consider how load is connected in defining R_{IN}

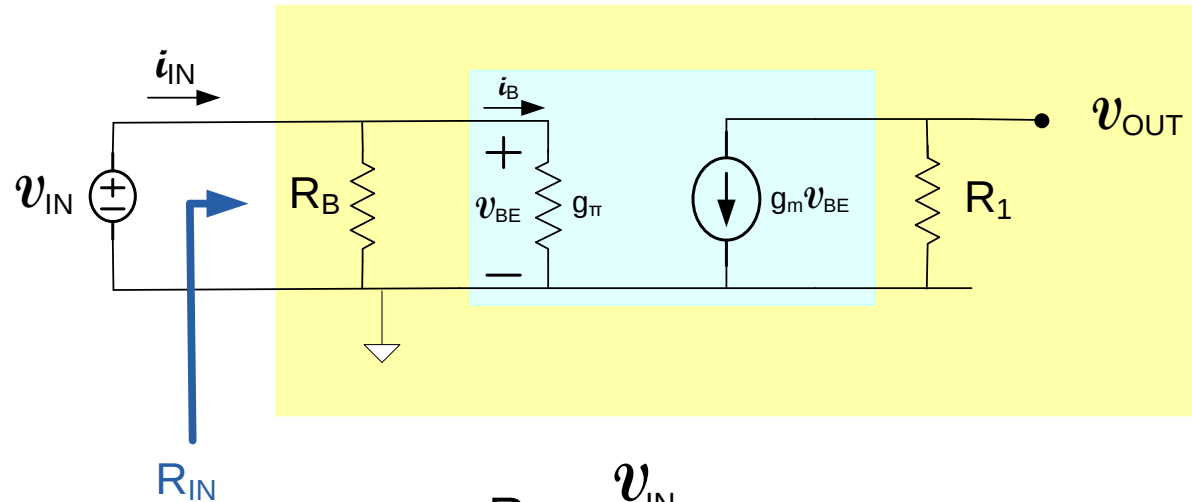


Amplifier Characterization (an example)

Determine R_{IN}



$\beta=100$



$$R_{in} = \frac{v_{IN}}{i_{IN}}$$

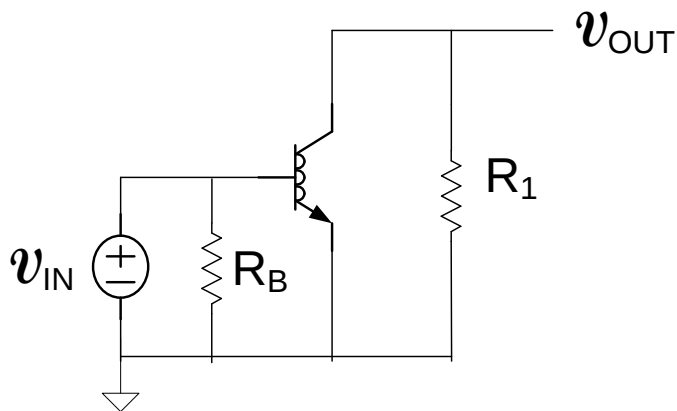
$$R_{in} = R_B // r_{\pi}$$

Usually $R_B \gg r_{\pi}$

$$R_{in} = R_B // r_{\pi} \cong r_{\pi}$$

$$R_{in} \cong r_{\pi} = \left(\frac{I_{CQ}}{\beta V_{t-1}} \right)^{-1}$$

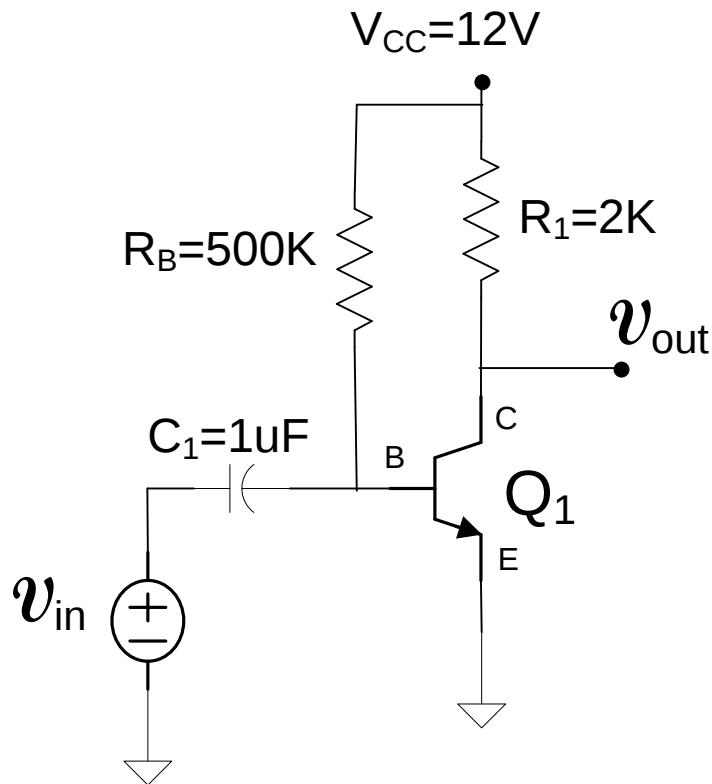
$$R_{in} \cong \left(\frac{2.3\text{mA}}{100 \cdot 25\text{mV}} \right)^{-1} = 1087\Omega$$



ss equivalent circuit

Amplifier Characterization (an example)

Determine v_{OUT} and $V_{OUT}(t)$ if $v_{IN} = .002\sin(400t)$



$$v_{OUT} = A_V v_{IN}$$

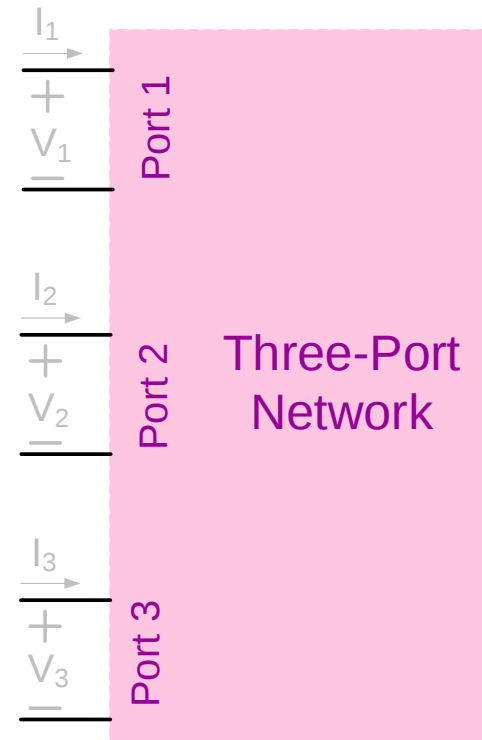
$$v_{OUT} = -177 \cdot .002 \sin(400t) = -0.354 \sin(400t)$$

$$V_{OUT}(t) \cong V_{OUTQ} + A_V v_{IN}$$

$$V_{OUT} \cong 7.4V - 0.35 \cdot \sin(400t)$$

This example identified several useful characteristics of amplifiers
but a more formal method of characterization is needed!

Two-Port and Three-Port Networks



- Each port characterized by a pair of nodes (terminals)
- Can consider any number of ports
- Can be linear or nonlinear but most interest here will be in linear n-ports
- Often one node is common for all ports
- Ports are externally excited, terminated, or interconnected to form useful circuits
- Often useful for decomposing portions of a larger circuit into subcircuits to provide additional insight into operation

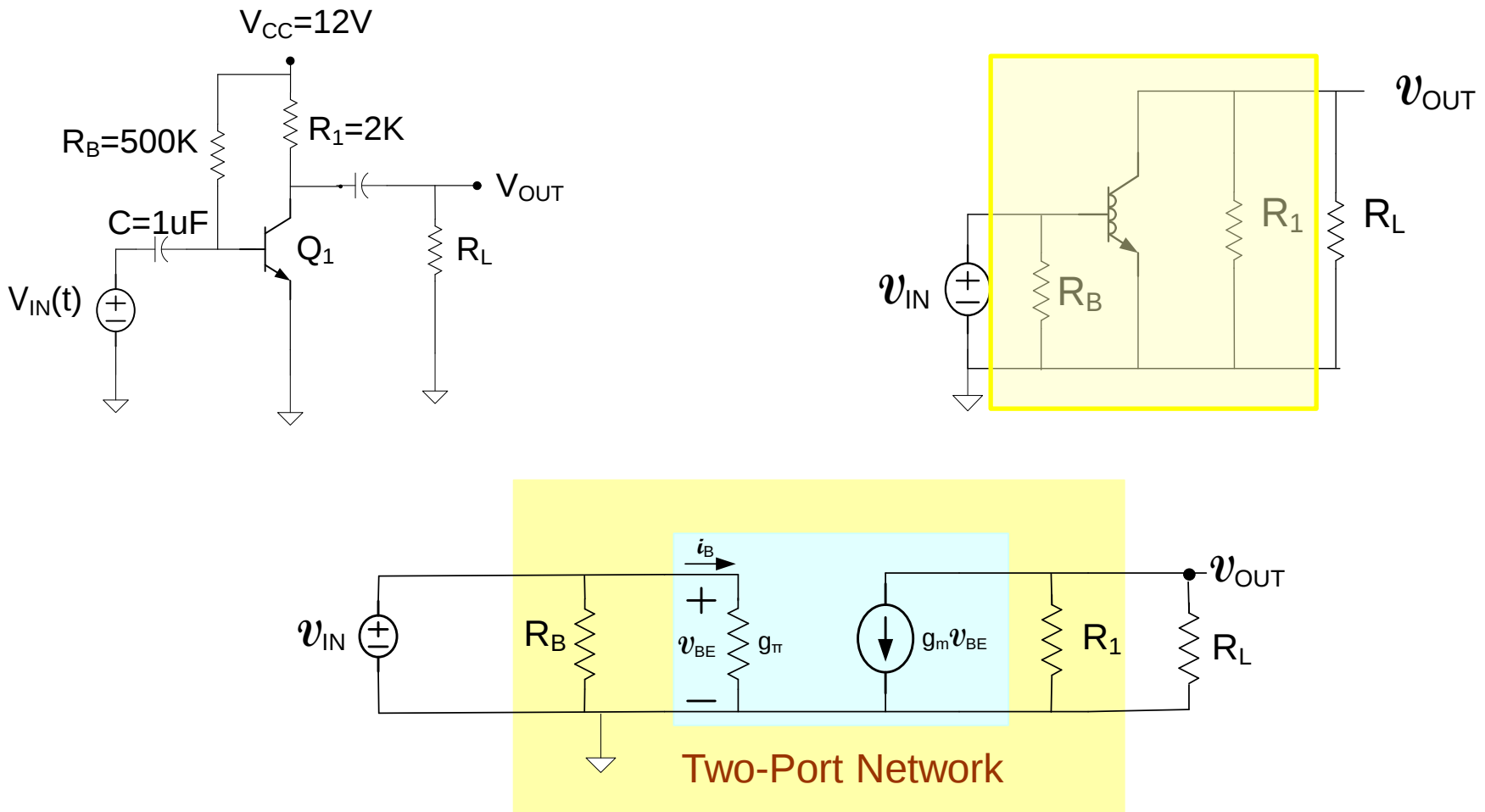
Amplifier Characterization

- Two-Port Models
- Amplifier Parameters

Will assume amplifiers have two ports, one termed an input port and the other termed an output port



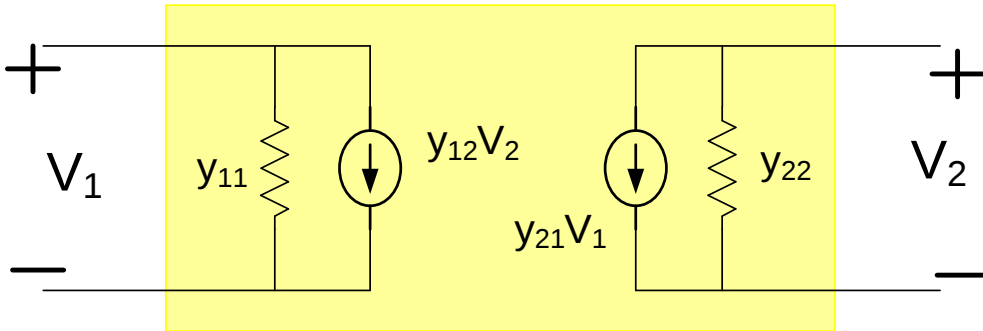
Two-Port Representation of Amplifiers



- Two-port model representation of amplifiers useful for insight into operation and analysis
- Internal circuit structure of the two-port can be quite complicated but equivalent two-port model (when circuit is linear) is quite simple

Two-port representation of amplifiers

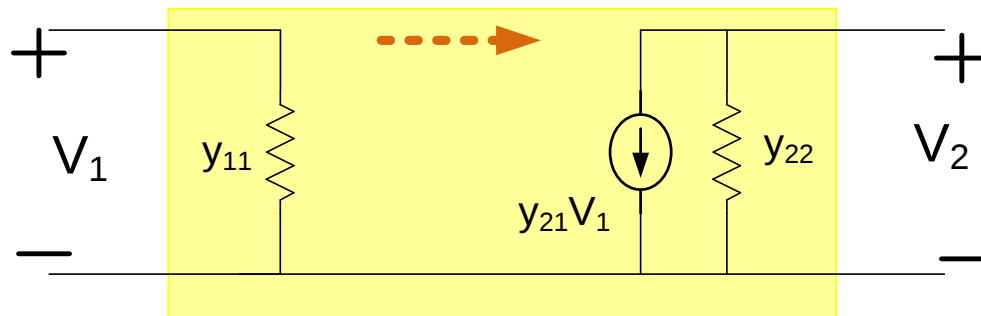
Amplifiers can be modeled as a linear two-port for small-signal operation



In terms of y-parameters

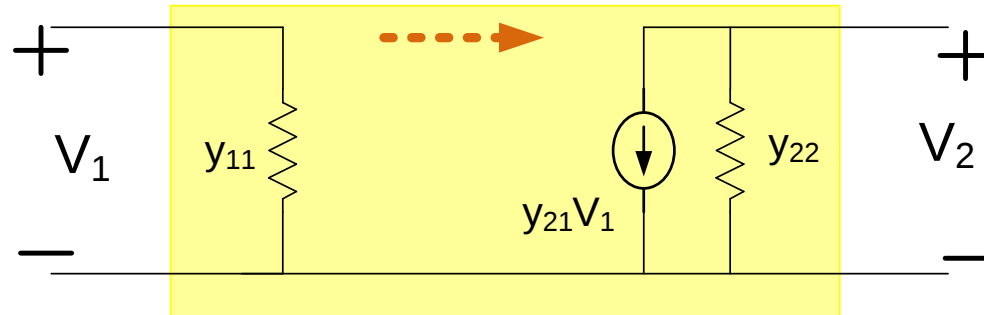
Other parameter sets could be used

- Amplifier often **unilateral** (signal propagates in only one direction: wlog $y_{12}=0$)
- One terminal is often common

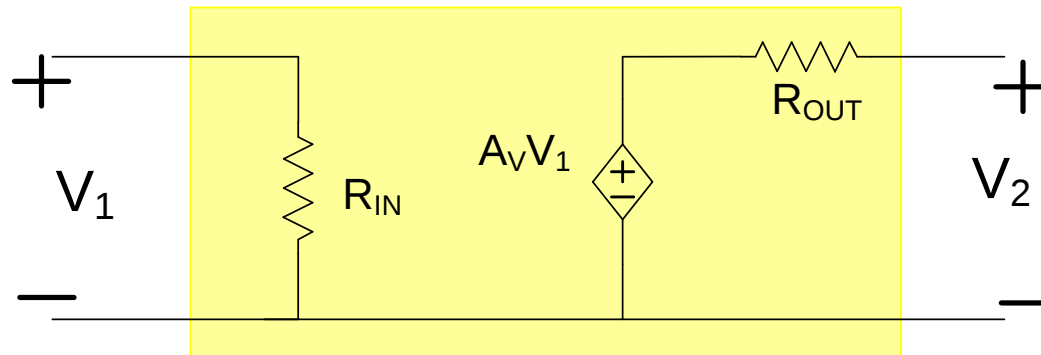


Two-port representation of amplifiers

Unilateral amplifiers:



- Thevenin equivalent output port often more standard
- R_{IN} , A_V , and R_{OUT} often used to characterize the two-port of amplifiers



Unilateral amplifier in terms of “amplifier” parameters

$$R_{IN} = \frac{1}{y_{11}}$$

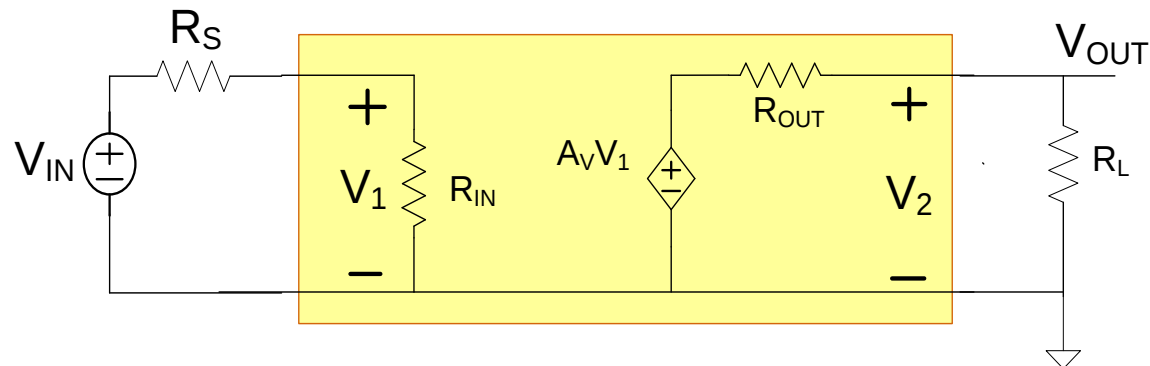
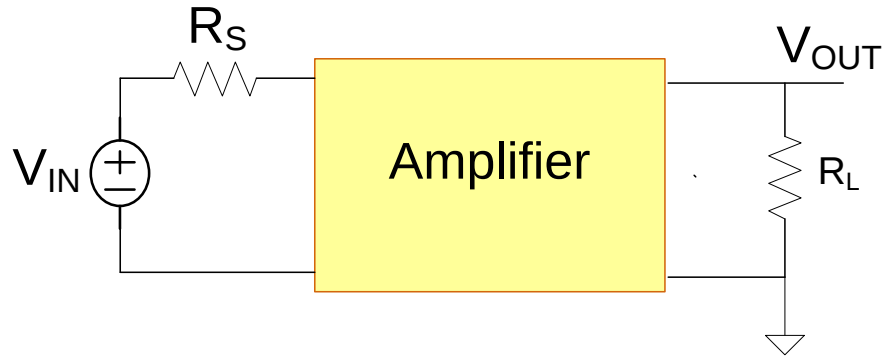
$$A_V = -\frac{y_{21}}{y_{22}}$$

$$R_{OUT} = \frac{1}{y_{22}}$$

Amplifier input impedance, output impedance and gain are usually of interest

Why?

Example 1: Assume amplifier is unilateral



$$V_{OUT} = \left(\frac{R_L}{R_L + R_{OUT}} \right) A_V \left(\frac{R_{IN}}{R_S + R_{IN}} \right) V_{IN}$$

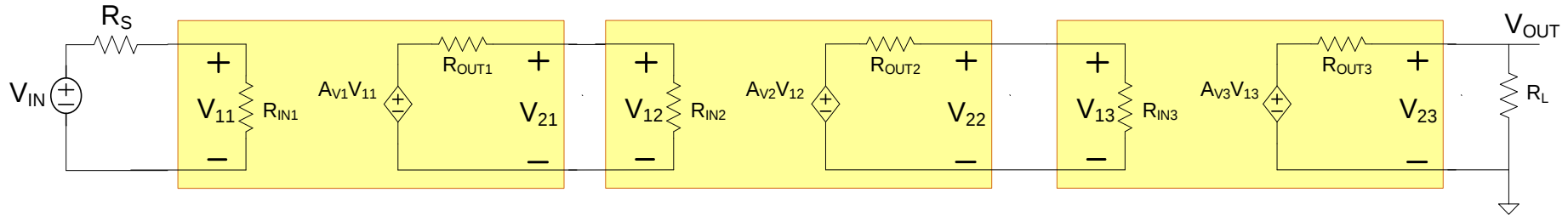
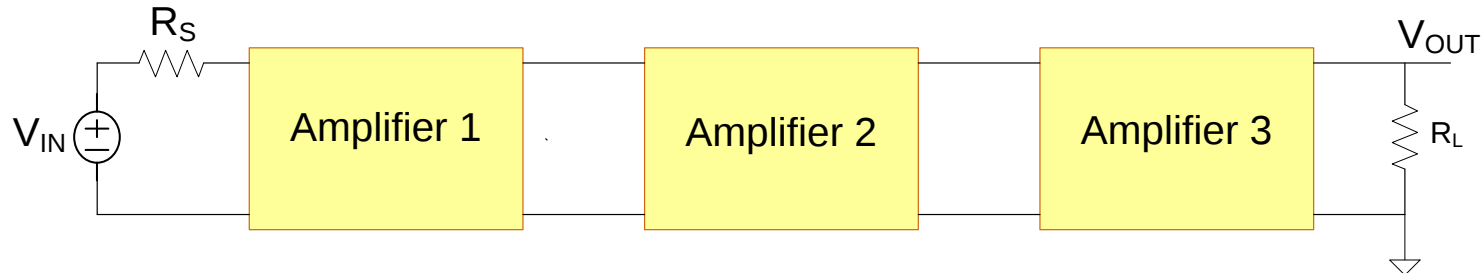
$$A_{VAMP} = \frac{V_{OUT}}{V_{IN}} = \left(\frac{R_L}{R_L + R_{OUT}} \right) \left(\frac{R_{IN}}{R_S + R_{IN}} \right) A_V$$

- Can get gain without reconsidering details about components internal to the Amplifier!!!
- Analysis more involved when not unilateral

Amplifier input impedance, output impedance and gain are usually of interest

Why?

Example 2: Assume amplifiers are unilateral



$$V_{OUT} = \left(\frac{R_L}{R_L + R_{OUT3}} \right) A_{V3} \left(\frac{R_{IN3}}{R_{OUT2} + R_{IN3}} \right) A_{V2} \left(\frac{R_{IN2}}{R_{OUT1} + R_{IN2}} \right) A_{V1} \left(\frac{R_{IN1}}{R_S + R_{IN1}} \right) V_{IN}$$

$$A_{VAMP} = \frac{V_{OUT}}{V_{IN}} = \left(\frac{R_L}{R_L + R_{OUT3}} \right) A_{V3} \left(\frac{R_{IN3}}{R_{OUT2} + R_{IN3}} \right) A_{V2} \left(\frac{R_{IN2}}{R_{OUT1} + R_{IN2}} \right) A_{V1} \left(\frac{R_{IN1}}{R_S + R_{IN1}} \right)$$

- Can get gain without reconsidering details about components internal to the Amplifier !!!
- Analysis more involved when not unilateral



Stay Safe and Stay Healthy !

End of Lecture 27